

International Workshop Meta-Optics and Metamaterials, IBS

Plasmonic Engineering in Subwavelength Space

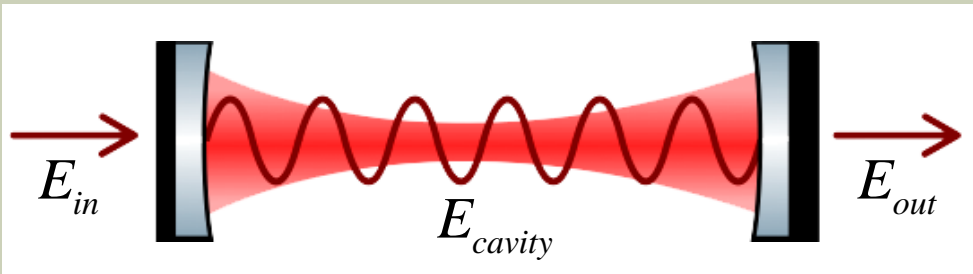
04/ 26/ 2018

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Converging Science and Technology

OPTICAL CAVITIES/RESONATORS



$$\frac{|E_{cavity}|^2}{|E_{in}|^2} = \left[\eta_{coupling} \cdot 4c \cdot \frac{A_{eff}}{n_{eff}} \right] \times \frac{Q}{V_m}$$

Small Volume
High Quality Factor

Various Applications with Optical Resonators

- *Small-Footprint, High-Performance Optical Communication Devices*
- *Lasers, Detectors, Modulators, Amplifiers etc.*
- *Highly-Sensitive Various Optical Sensors*
- *Efficient Single Photon Sources*
- *Metamaterials*

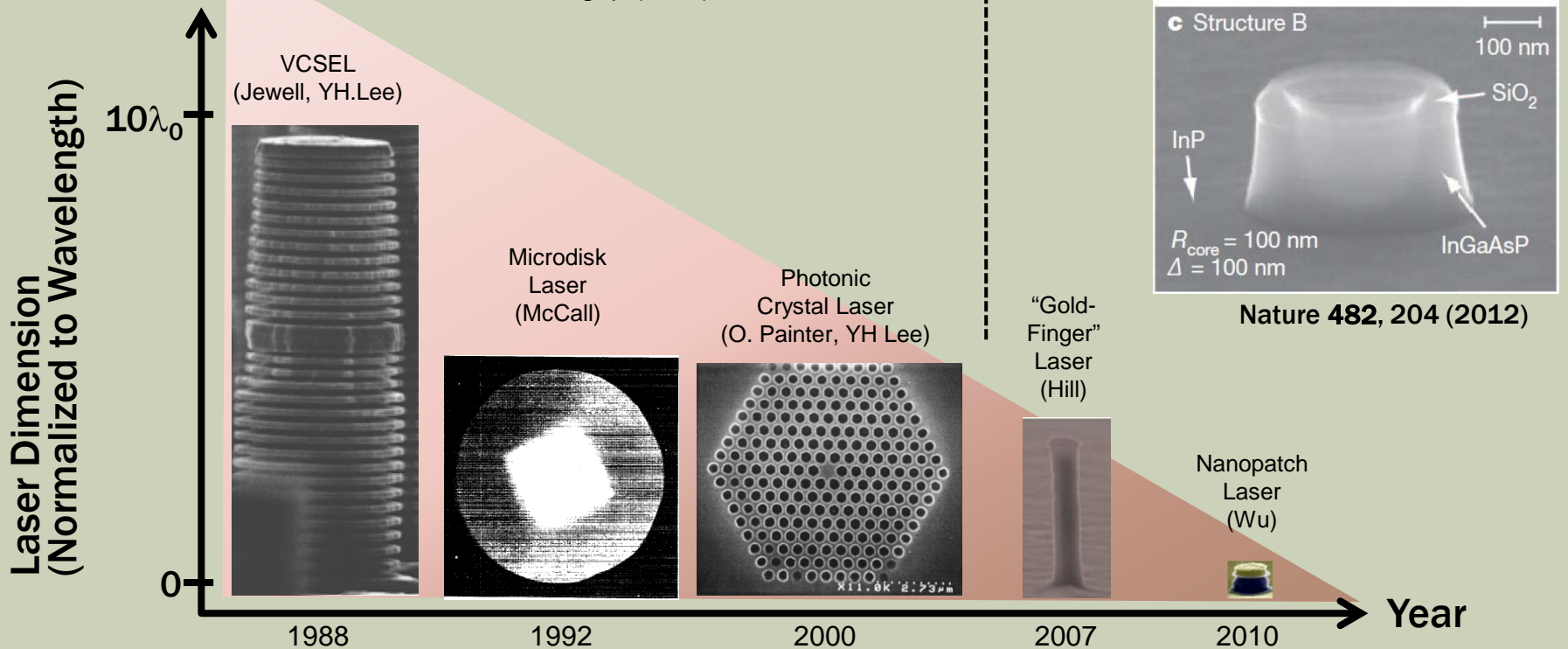
TOWARDS SMALLEST CAVITIES

Dielectric Cavity

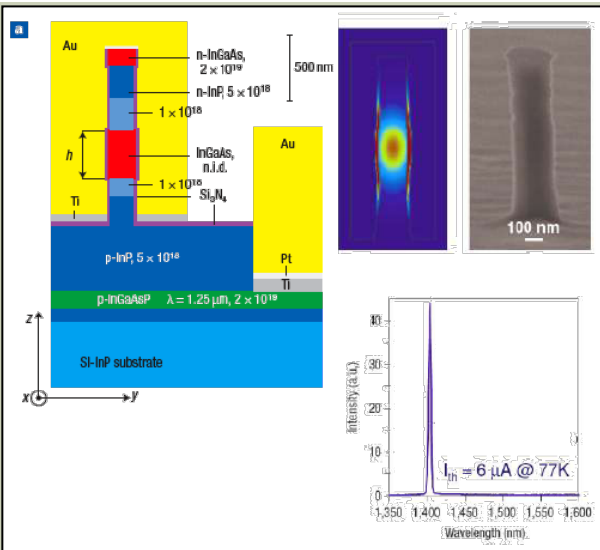
Total Internal Reflection (TIR)
Photonic Bandgap (PBG)

Plasmonic Cavity

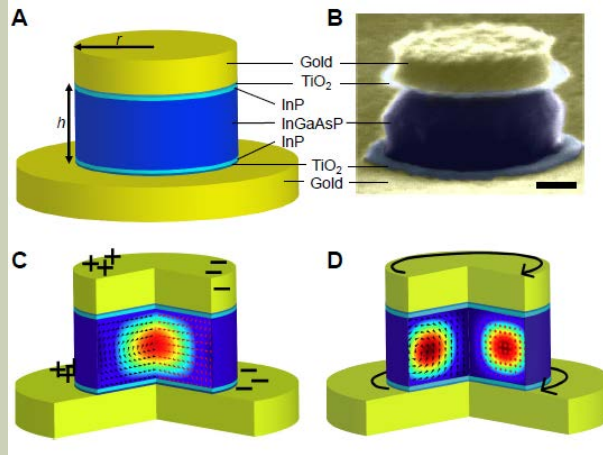
Surface Plasmon Polaritons (SPPs)



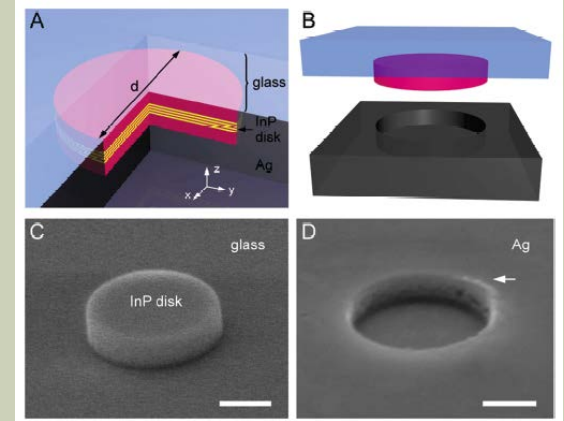
SUB-WAVELENGTH PLASMONIC CAVITIES



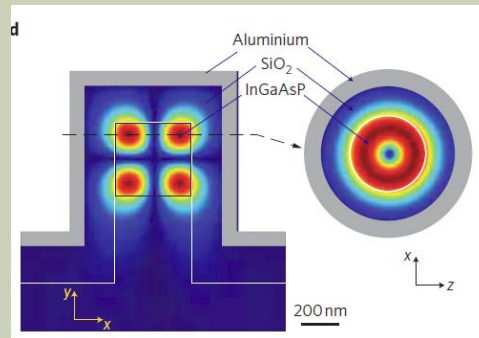
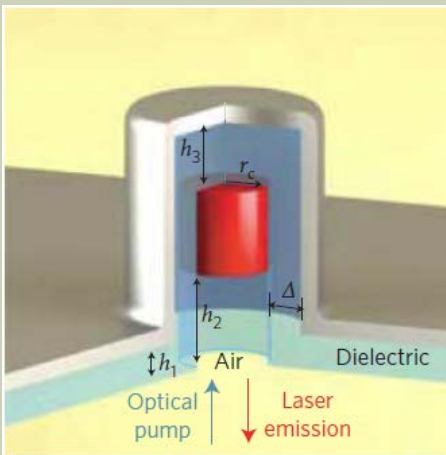
M. T. Hill et al, Nature Photon. (2007)



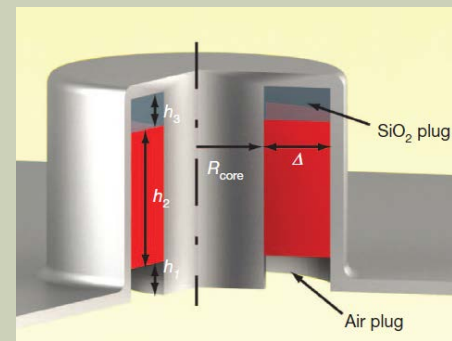
K.-S. Yu et al, Opt. Express (2010)



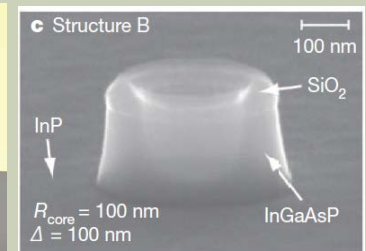
S.-H. Kwon et al., Nano Lett. (2010)



M. P. Zezhad et al, Nature Photon. (2010)



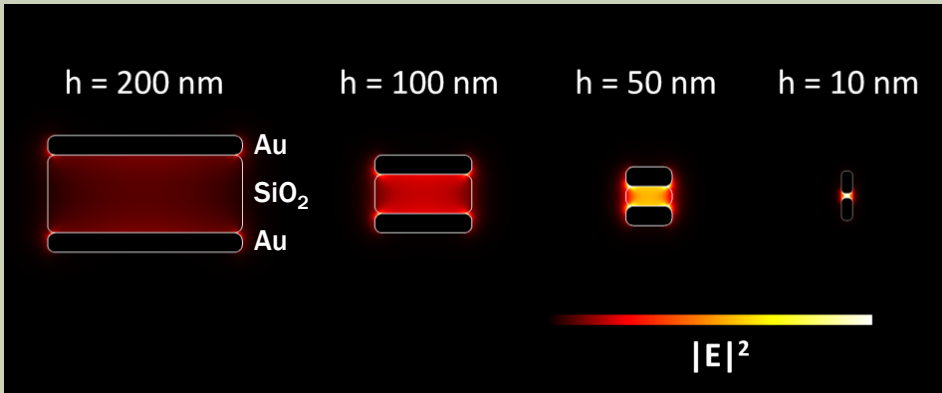
M. Khajavikhan et al., Nature (2012)



PLASMONIC CAVITY LASERS

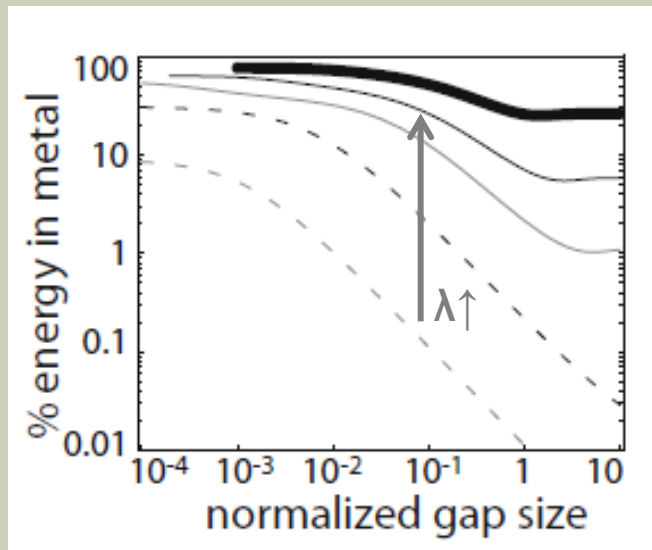
Type	Q (at RT)	V_{mode} $(\lambda/2n)^3$	Γ	Pump.	η_{coupling}	Temp. (K)
M. Hill	48 (gold)	0.38	43 %	Electrical	N.A.	10, 77K
NanoPatch (UCB)	65 (gold)	0.54	84 %	Optical	N.A.	77K
NanoPan (KAIST)	~110 (silver)	0.56	-	Optical	N.A.	8, 80K
UCSD	1004 (aluminum)	5.2	46 %	Optical	N.A.	300K
UCSD	300 (silver)	0.3	70 %	Optical	N.A.	4.5K

LARGE ABSORPTION LOSS BY METAL

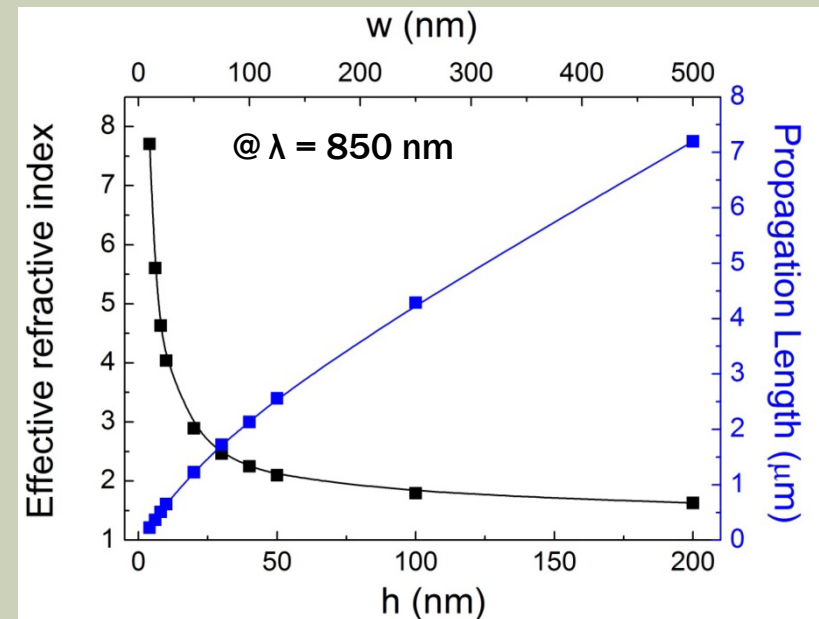


As dimension decreases, the absorption loss and k -vector are highly increased.

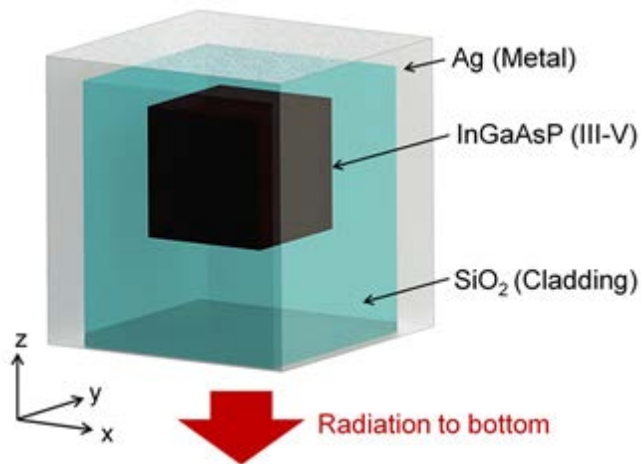
We should find the best way to minimize the losses at this large- k regime



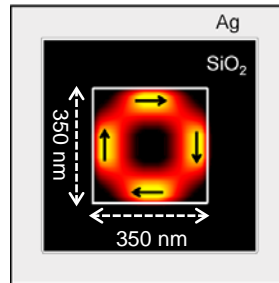
S. Maier, "Plasmonics" (2007)



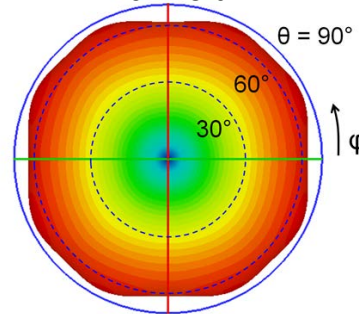
DIFFICULTY IN COUPLING W/ WAVEGUIDE



Near-field

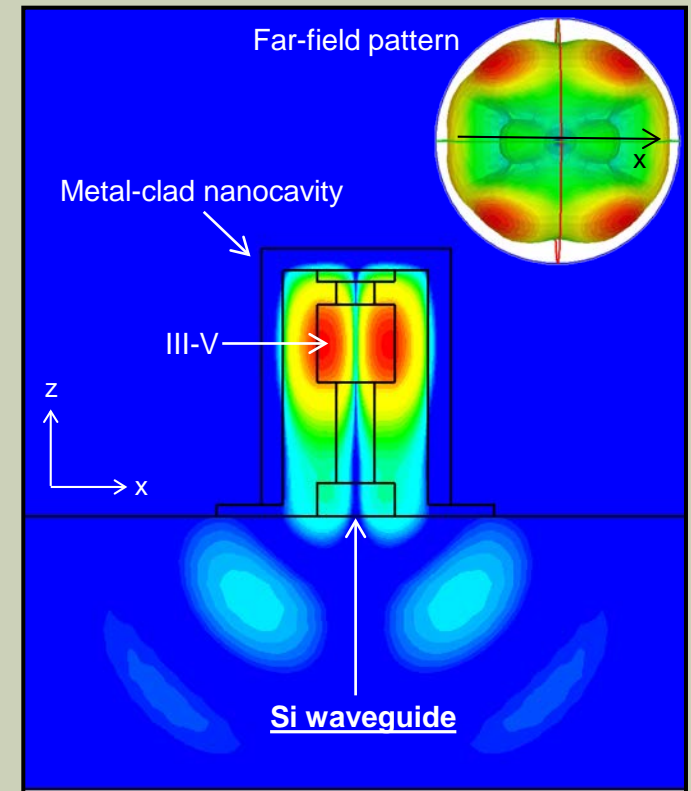


Far-field



Because of the **extremely small output aperture** of such a cavity, the **radiation from the cavity diverges very rapidly**.

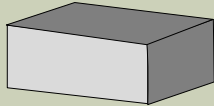
Coupling efficiency with Si waveguide < 10 %



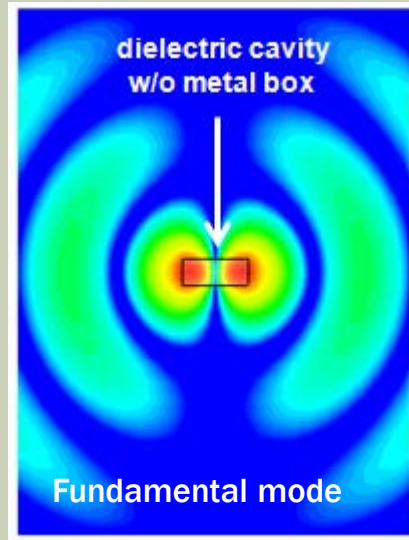
CLADDING ENGINEERING
FOR HIGH-Q AND LARGE COUPLING

METALLIC BOX CAVITY

Dielectric Semiconductor Cavity

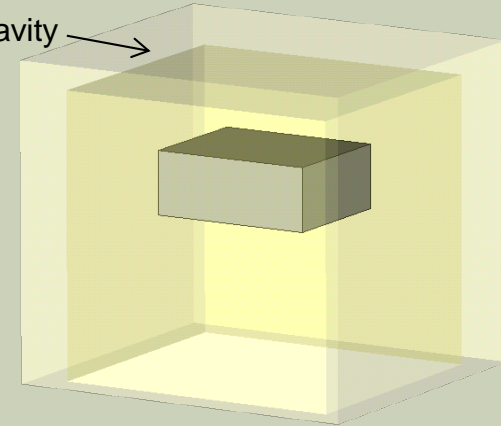


(500nm × 400nm × 200nm)

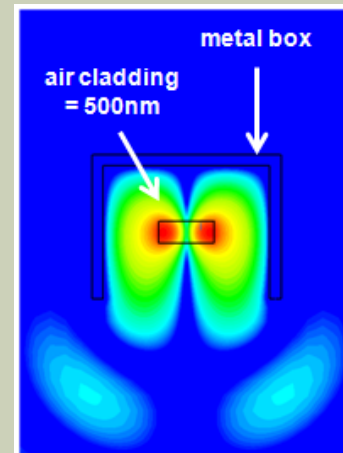


$$Q = 8$$
$$V_m = 0.35 (\lambda/n)^3$$

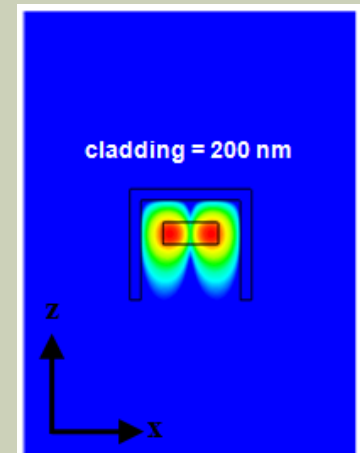
Metal-clad cavity



Radiation is
suppressed
by metal



$$Q = 75$$
$$V_m = 0.29 (\lambda/n)^3$$



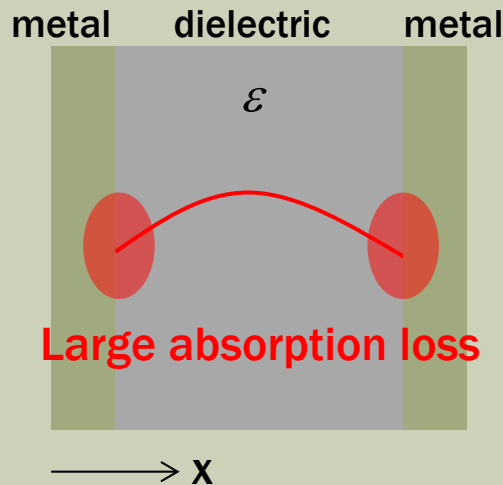
$$Q = 3100$$
$$V_m = 0.25 (\lambda/n)^3$$

REDUCING ABSORPTION LOSSES WITH LOW-INDEX CLADDINGS

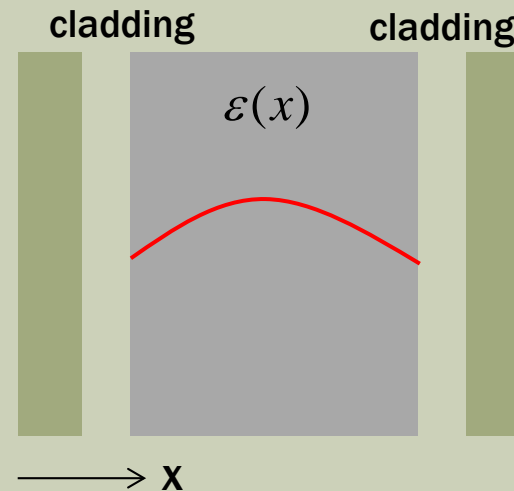
1D wave-equation

$$\left[\frac{\partial^2}{\partial x^2} + \omega^2 \mu_0 \varepsilon \right] \psi(x) = 0$$

$$\left[\frac{\partial^2}{\partial x^2} + \omega^2 \mu_0 \varepsilon(x) \right] \psi(x) = \left[\frac{\partial^2}{\partial x^2} + V(x) \right] \psi(x) = 0$$

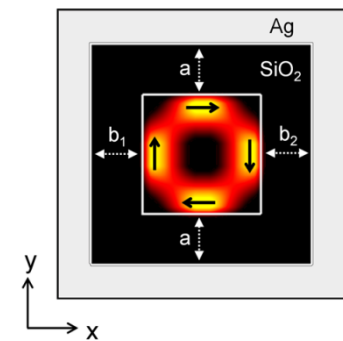
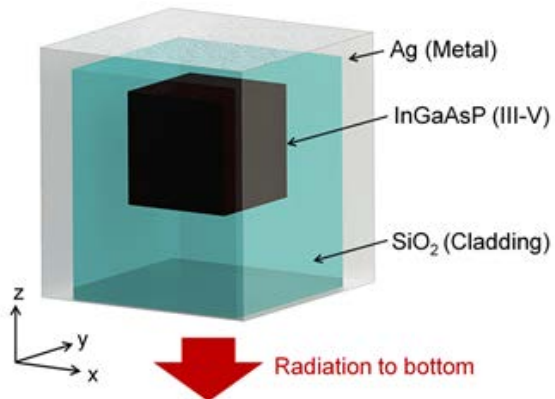


High Reflection (High Q_{rad})
Large Absorption (Low Q_{abs})

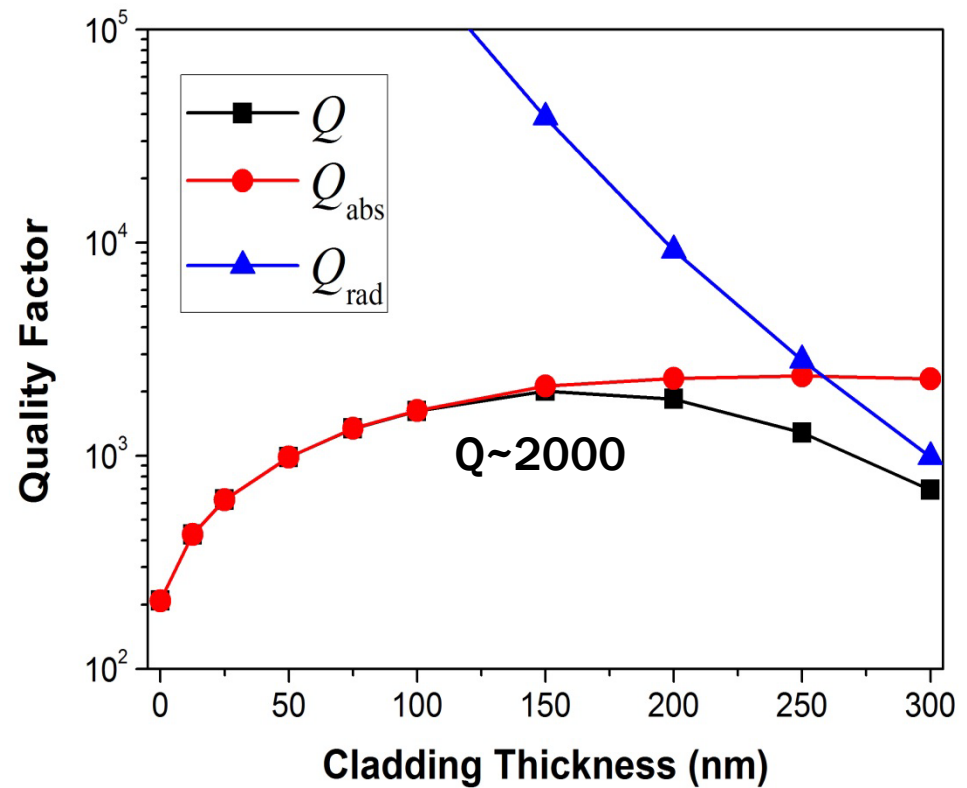


High Reflection (High Q_{rad})
Small Absorption ($Q_{\text{abs}} \uparrow$)

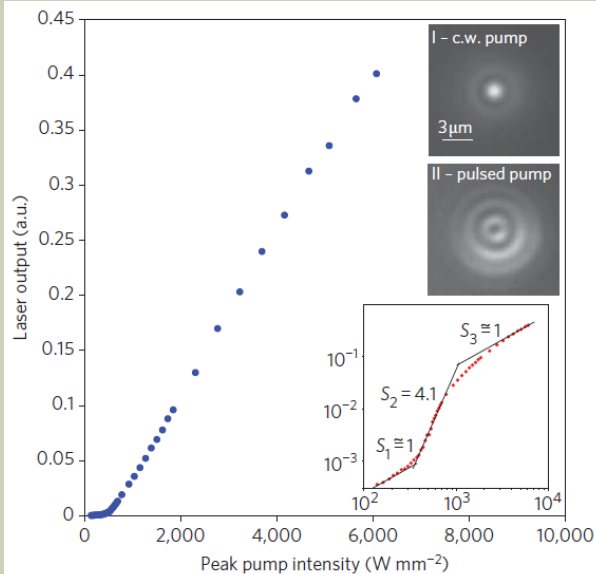
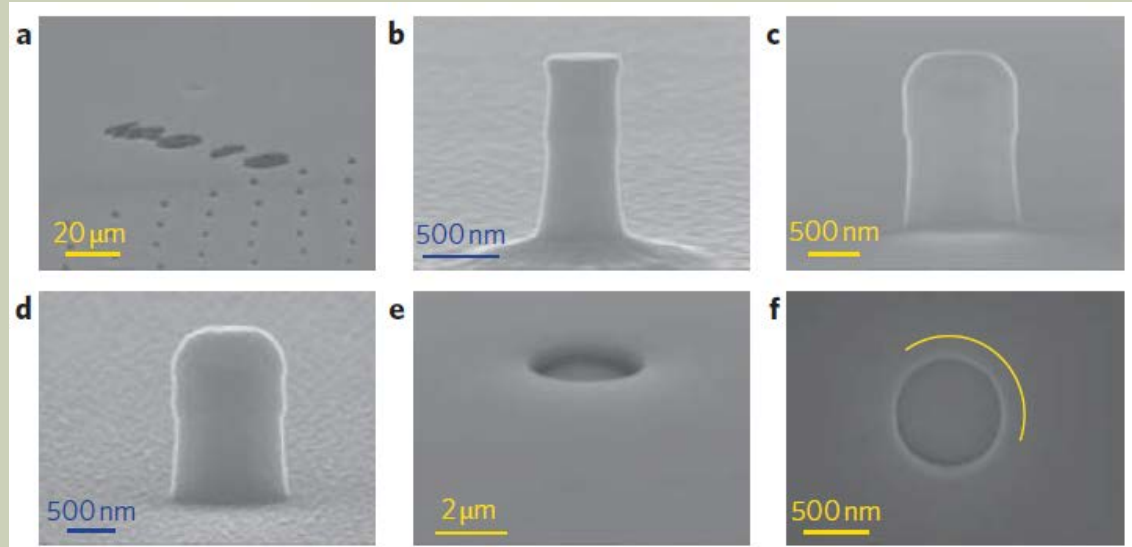
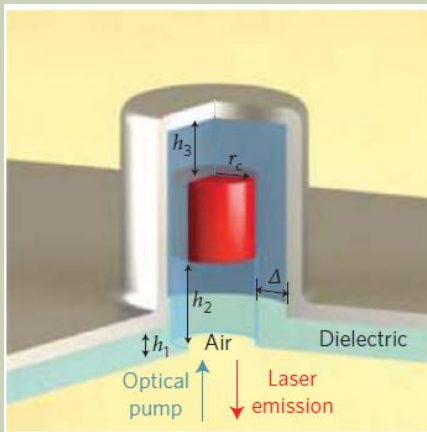
Q VS. CLADDING THICKNESS



$a = b_1 = b_2 = \text{cladding thickness}$

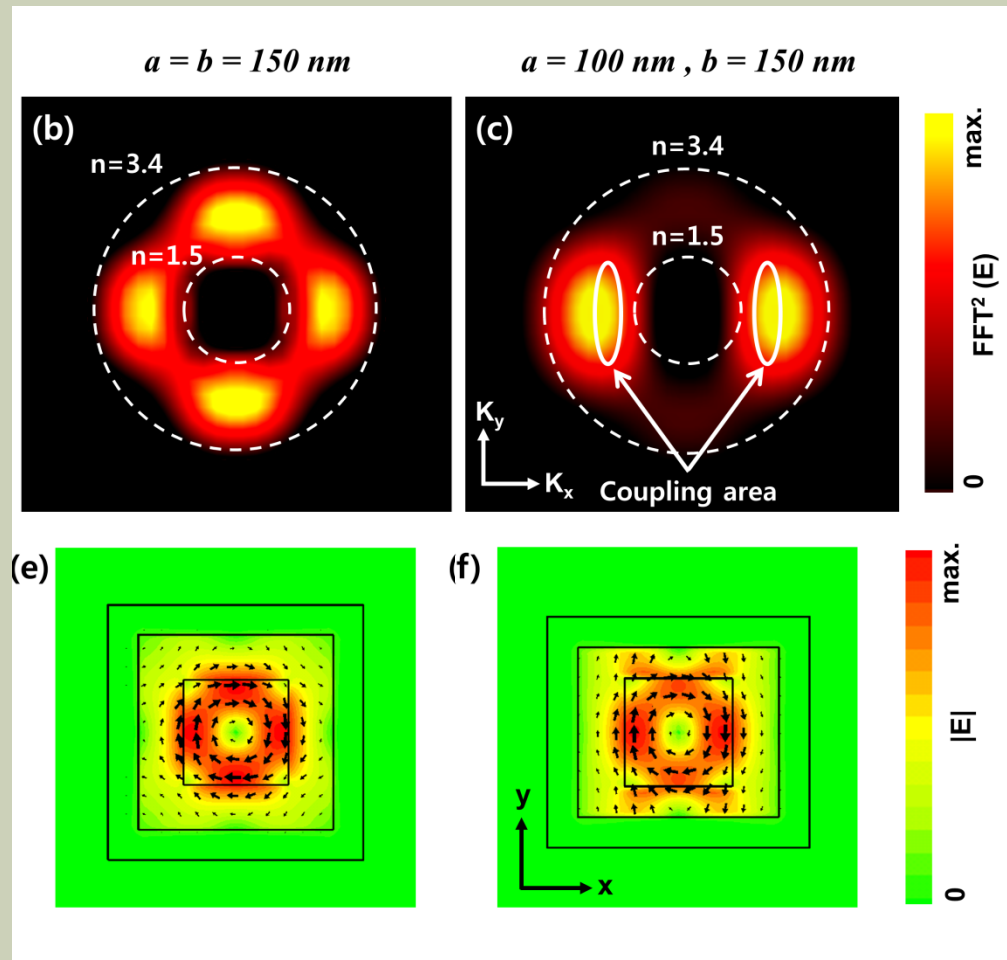


METAL-CLAD CAVITY LASER

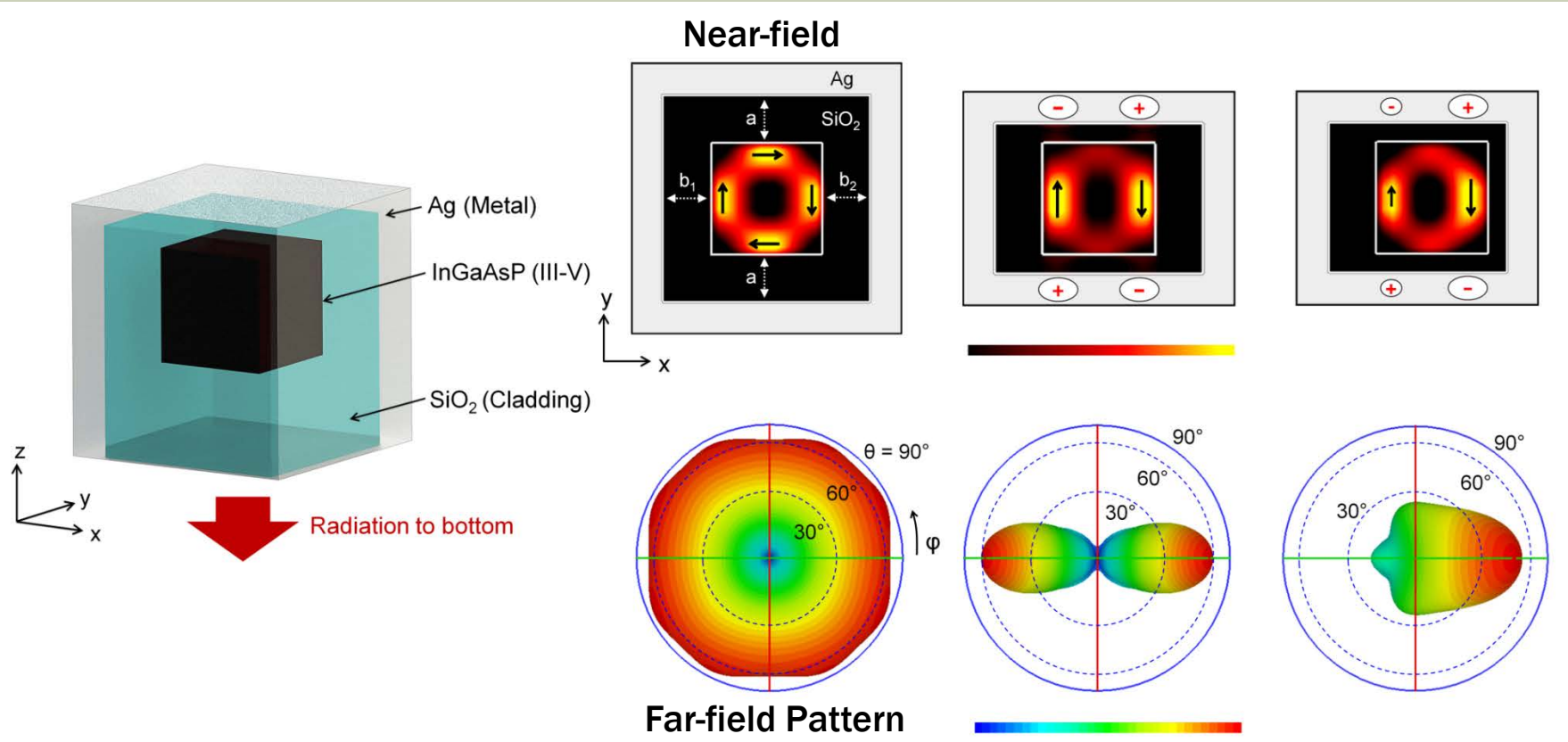


They demonstrated **room-temperature pulsed laser emission** from optically pumped metallo-dielectric cavities

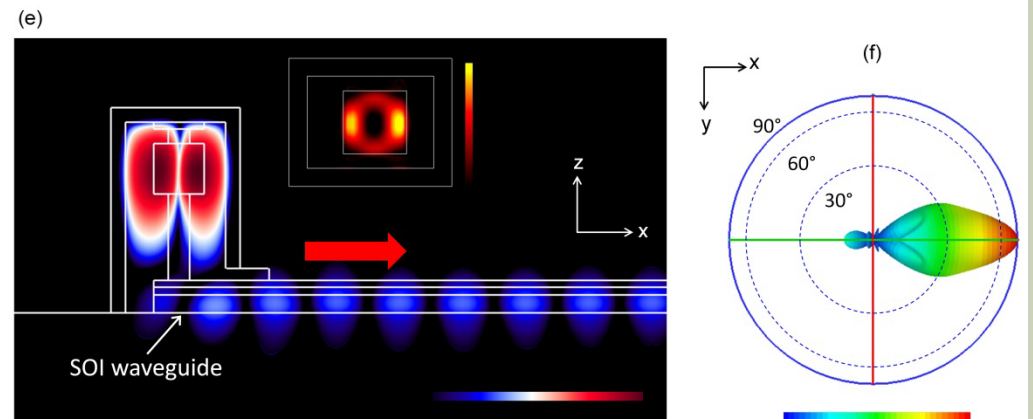
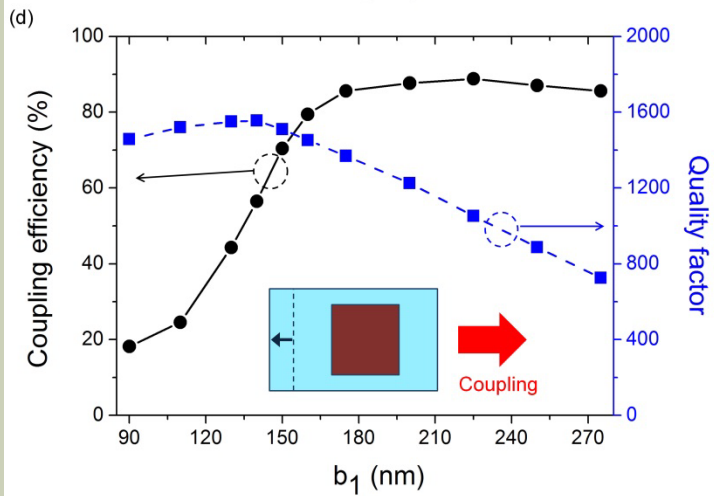
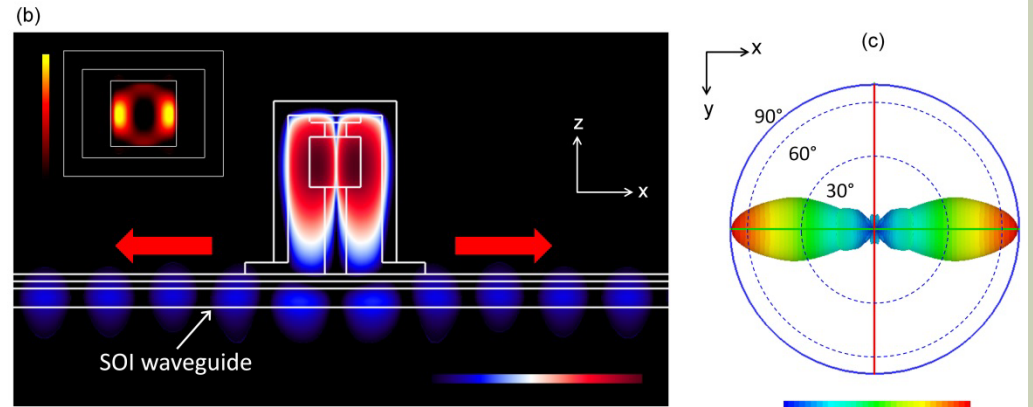
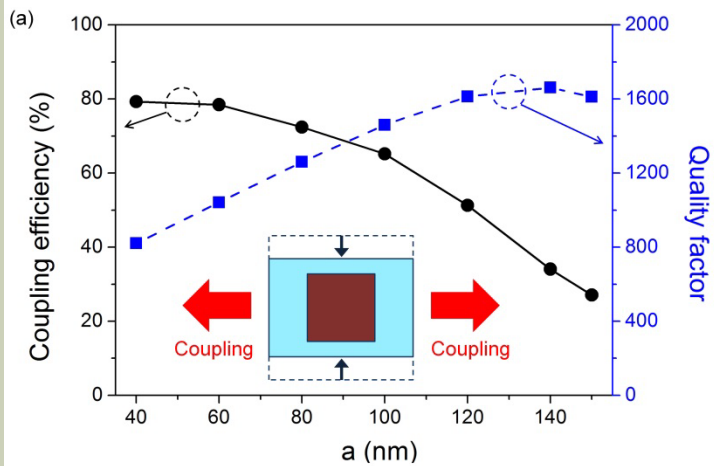
FOR THE EFFICIENT COUPLING



BI-/UNI-DIRECTIONAL RADIATION



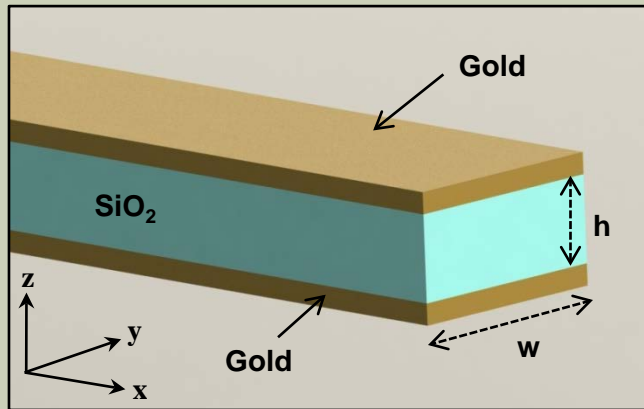
EFFICIENT COUPLING IN SI/III-V INTEGRATION



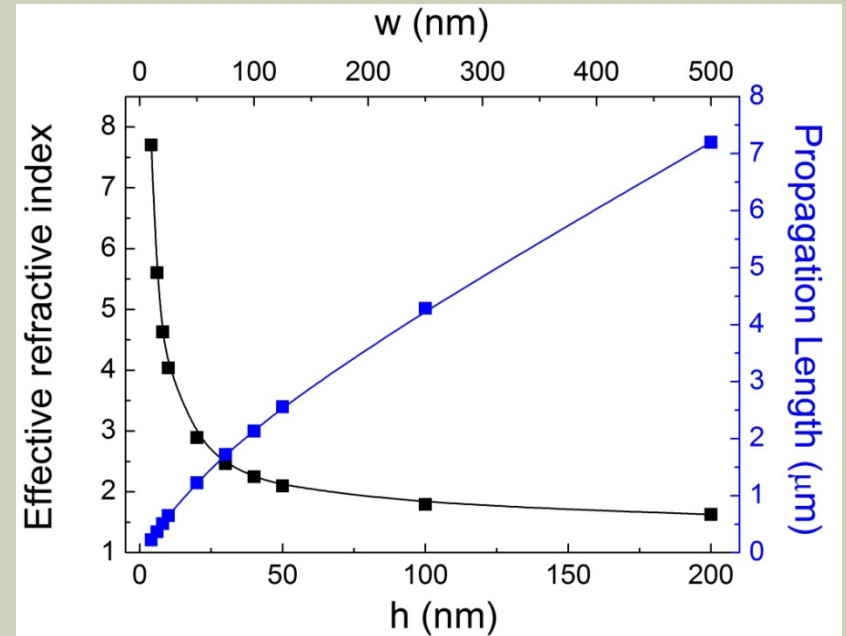
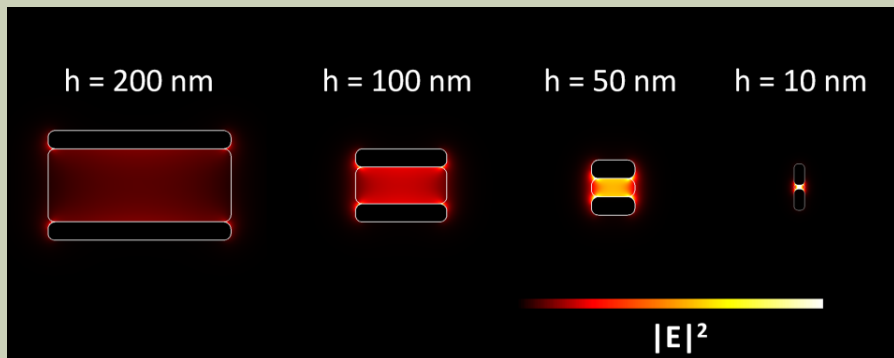
GEOMETRIC ENGINEERING
FOR EXTREME PHOTON SQUEEZING

METAL-INSULATOR-METAL PLASMONIC MODE

Metal-insulator-metal (MIM) Plasmonic Mode



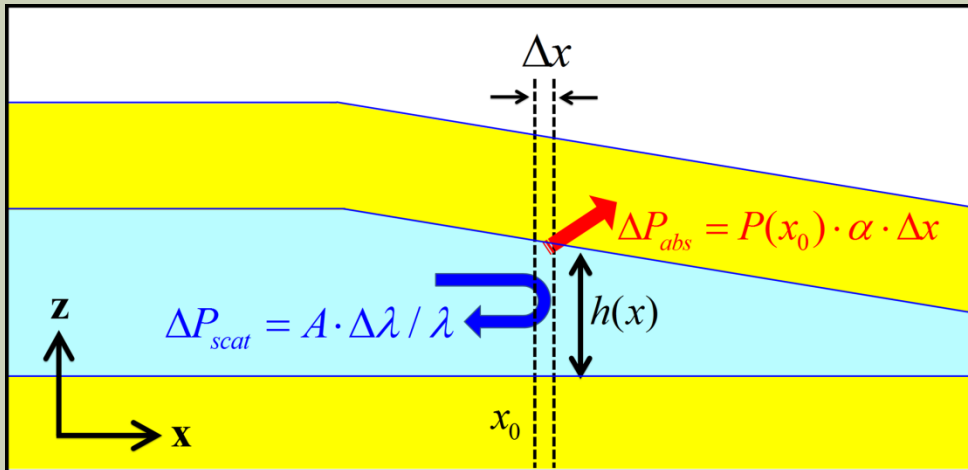
$$w/h = 500 \text{ nm} / 200 \text{ nm}, \quad \lambda = 830 \text{ nm}$$



No cut-off dimension (Limitless confinement)

But, Significant Loss at Large- k Regime

OPTIMAL GEOMETRY FOR MINIMIZING LOSSES



At large-k approximation

$k \cdot h = f(\omega)$: dispersion relation

$\Delta x \sim \lambda$

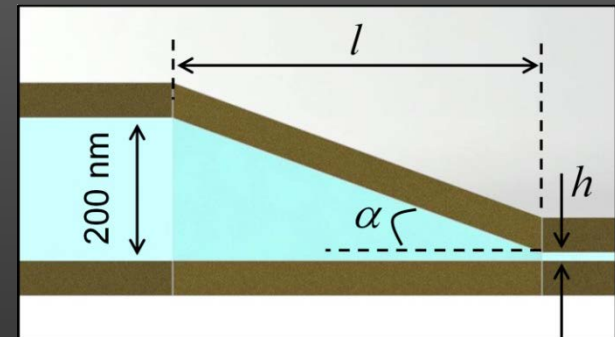
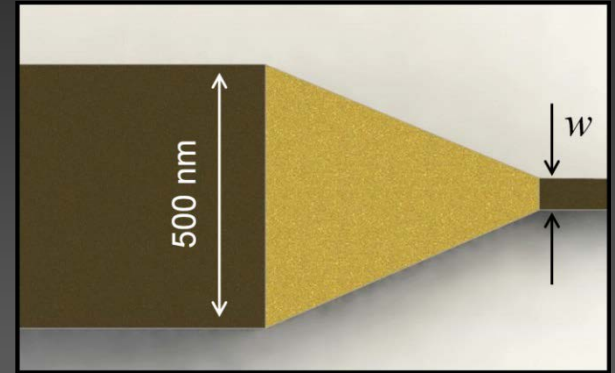
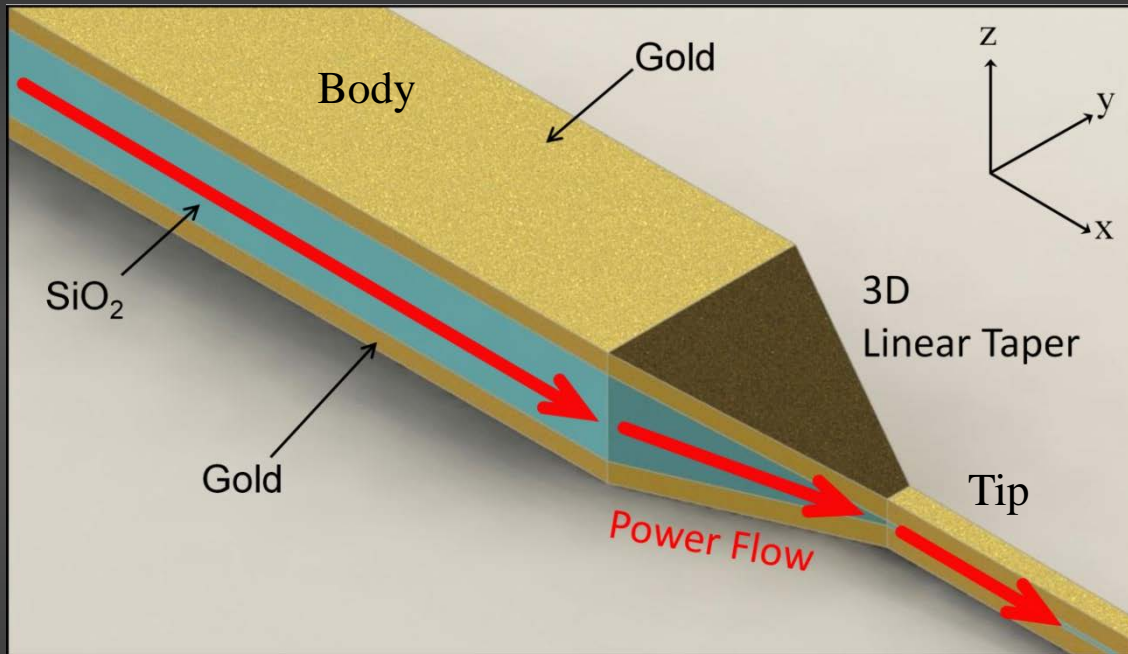
$$\begin{aligned}\Delta P_{loss} &= \Delta P_{scat} + \Delta P_{abs} \\ &= A \cdot \Delta\lambda / \lambda + P_0 \cdot \alpha \cdot \Delta x \\ &= A \cdot \Delta\lambda / \lambda + B \cdot \text{Im}[k] \cdot \Delta x\end{aligned}$$

$$\begin{aligned}\Delta P_{loss} &\approx A \cdot (\Delta h / \Delta x) + B \cdot \text{Im}[k] \cdot \lambda \\ &= A \cdot (\Delta h / \Delta x) + C = \text{constant}\end{aligned}$$

So, “linear-taper geometry”
minimizes the losses generated in
MIM structure.

Highly Efficient 3D On-Chip Nanofocusing Device

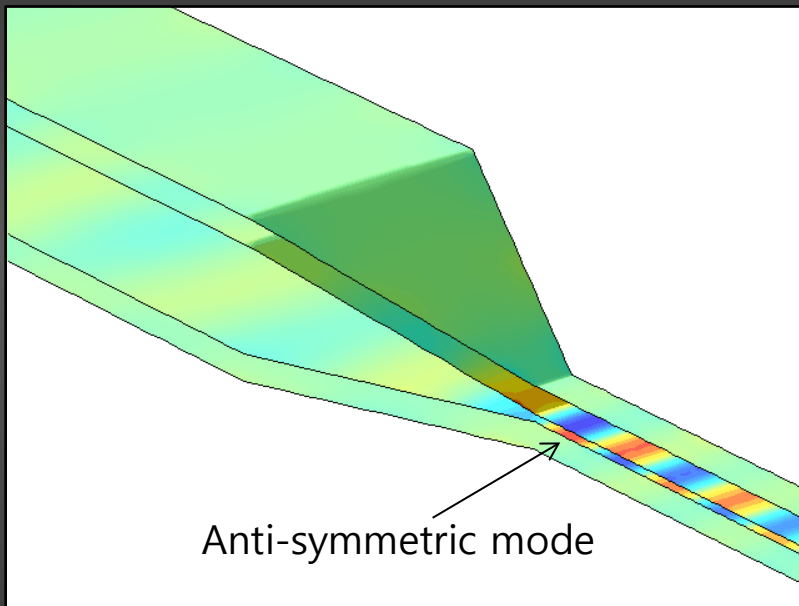
Design of 3D MIM Plasmonic Nanofocusing Device



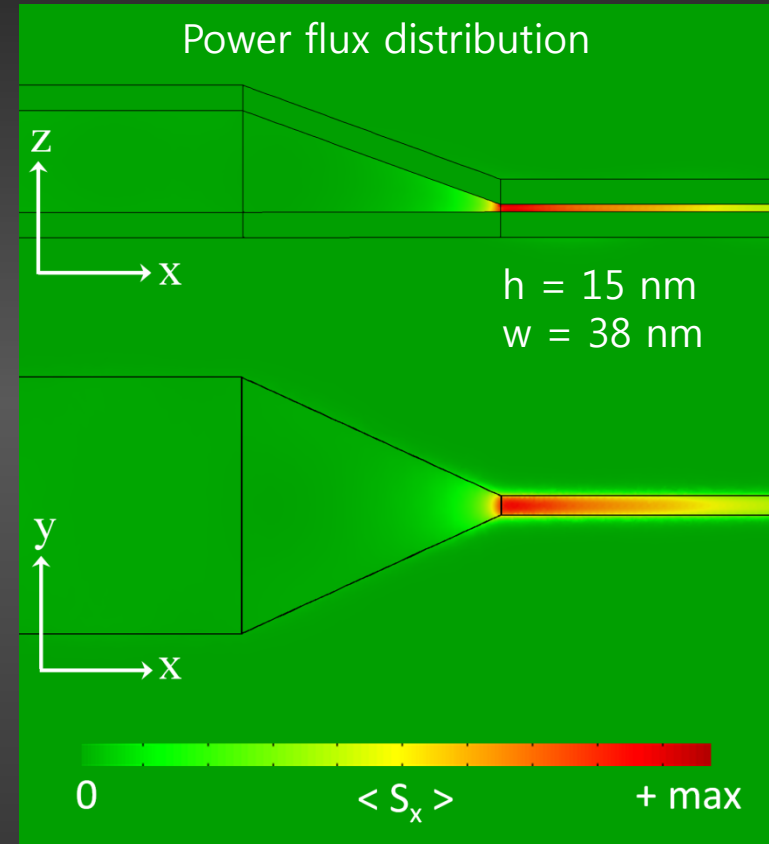
M. Kim, H. Choo, E. Yablonovitch et al. Nature Photonics 6, 838 (2012)

Highly Efficient 3D On-Chip Nanofocusing Device

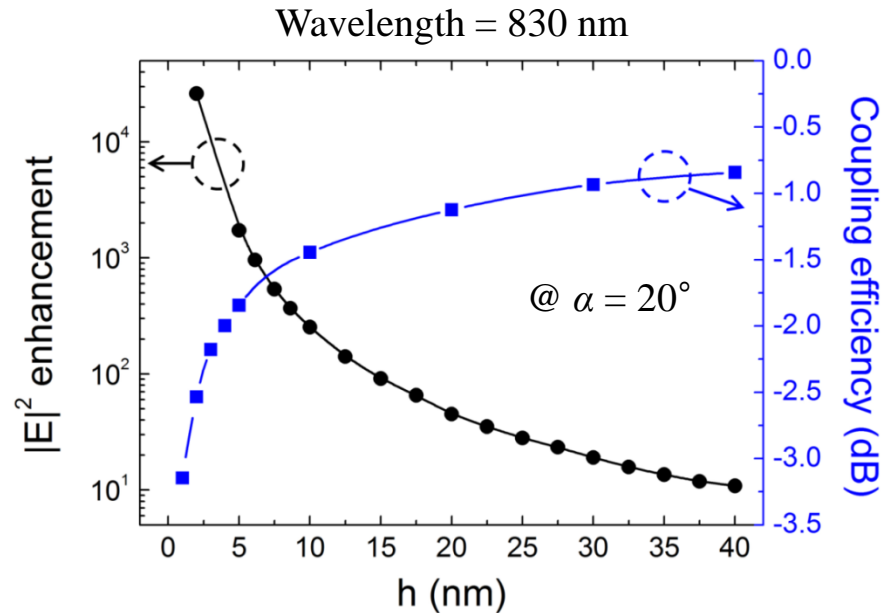
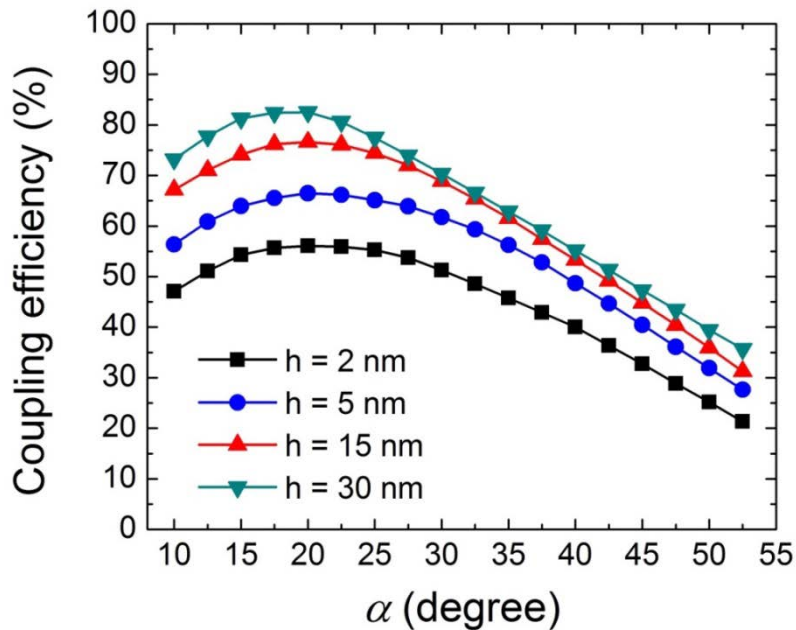
Surface-charge density propagation



Power flux distribution



Highly Efficient 3D On-Chip Nanofocusing Device

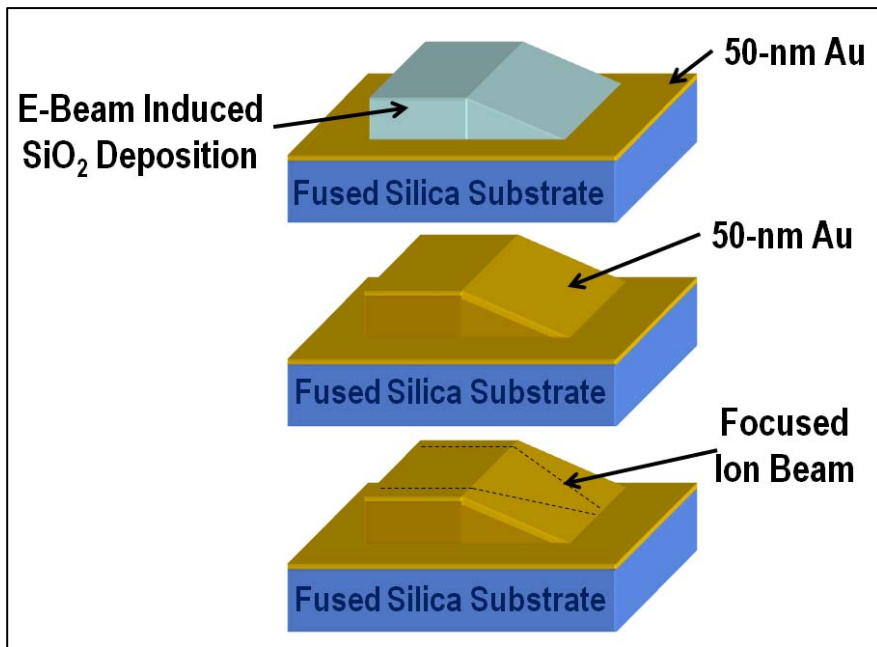


Optimal coupling angle: $10^\circ < a < 30^\circ$

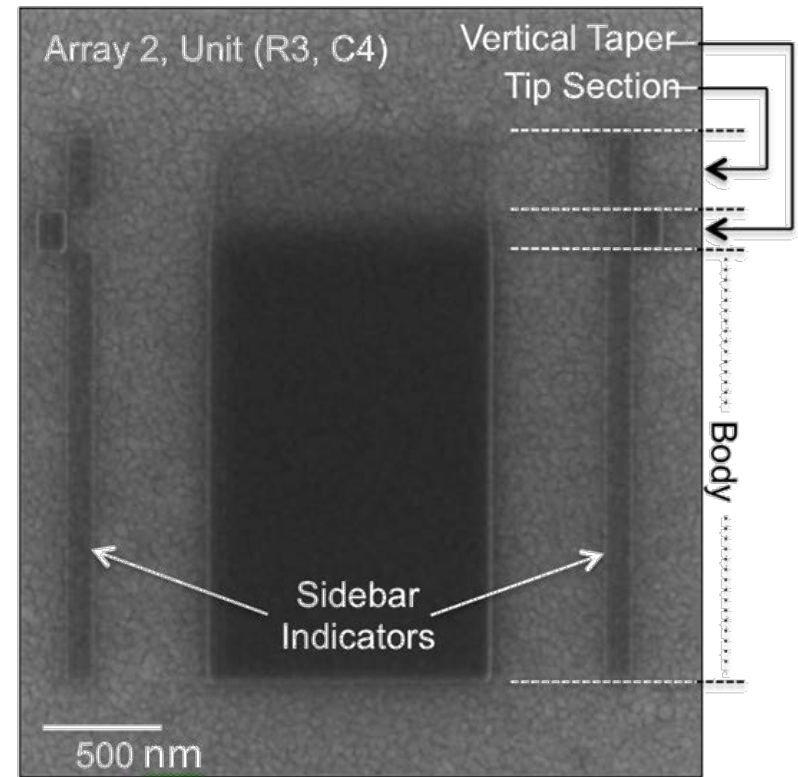
When focusing into $2 \times 5 \text{ nm}^2$ area,
Coupling loss = 2.5 dB
 E^2 enhancement $\sim 3.0 \times 10^4$

Fabrications

Fabrication Steps

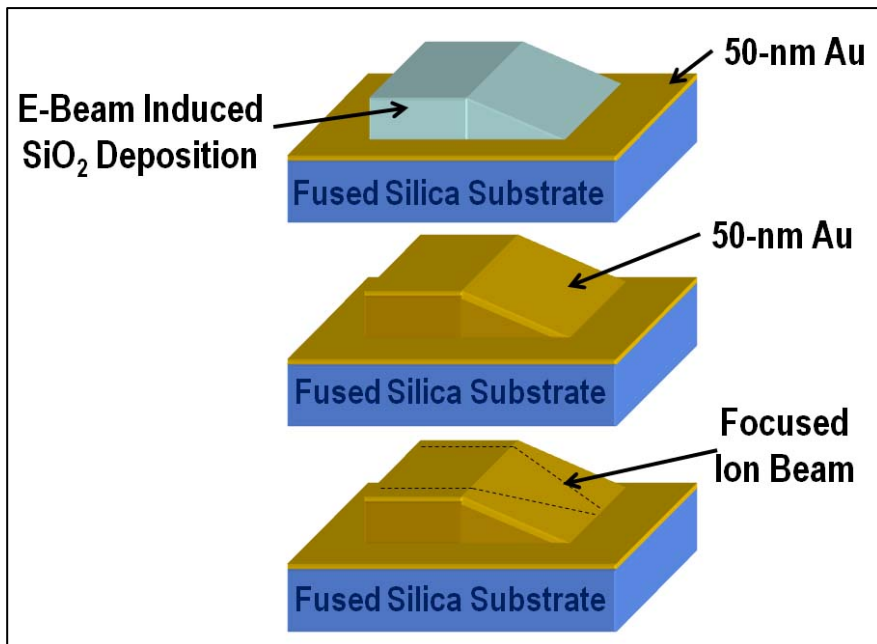


E-beam induced SiO₂ deposition on Au

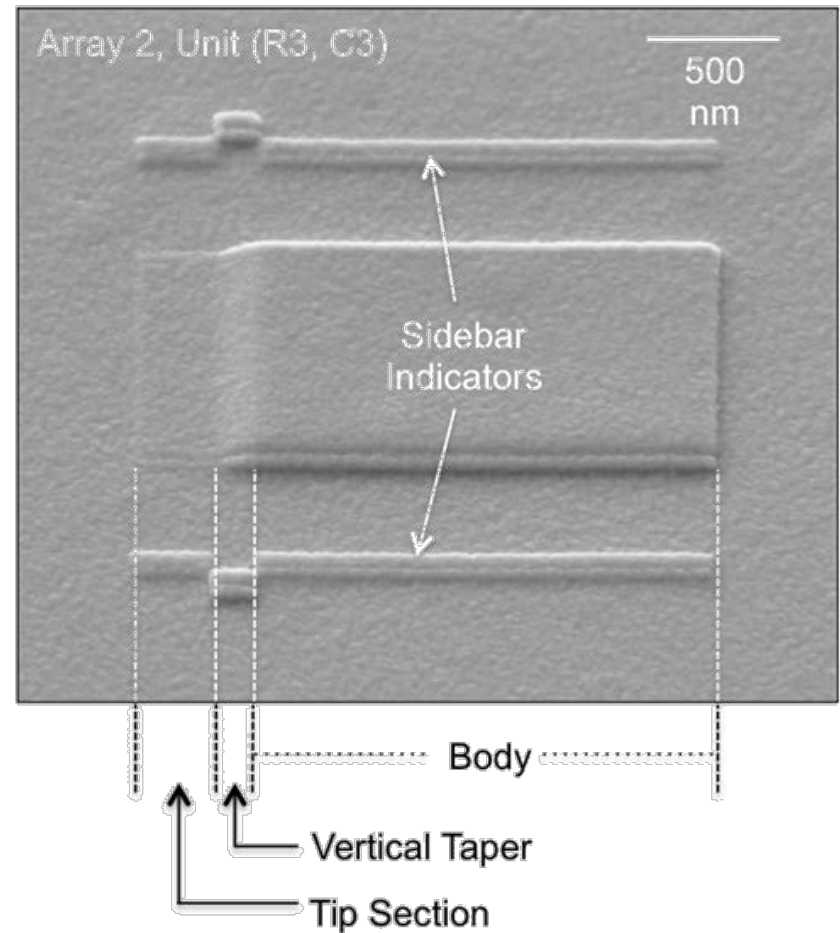


Fabrications

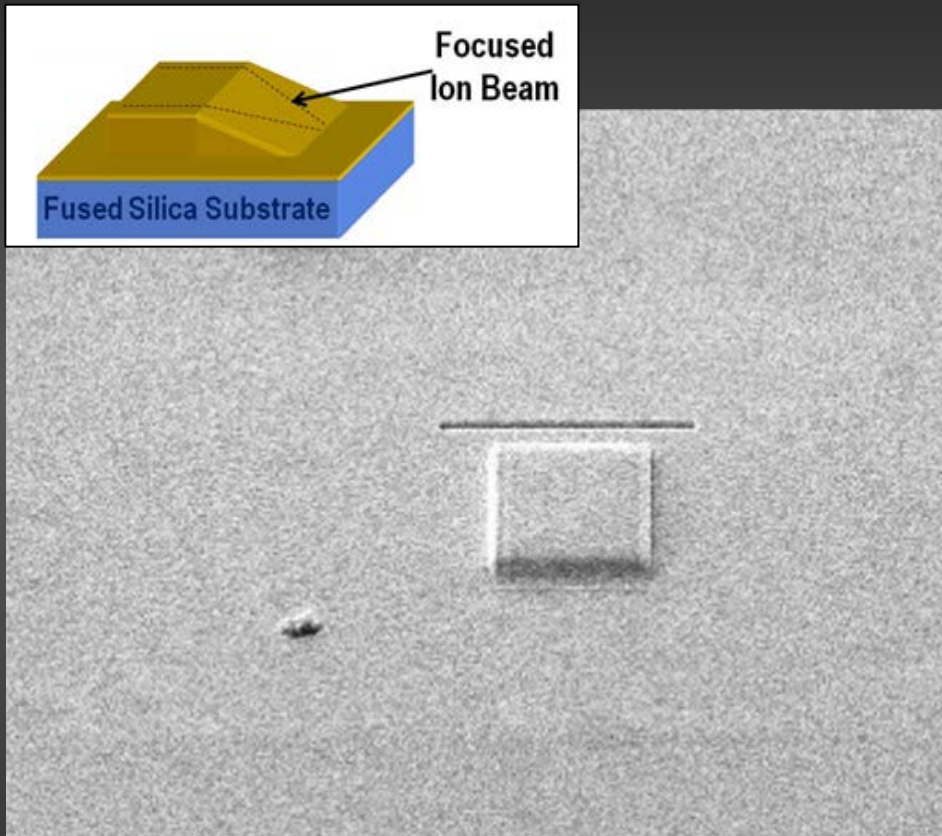
Fabrication Steps



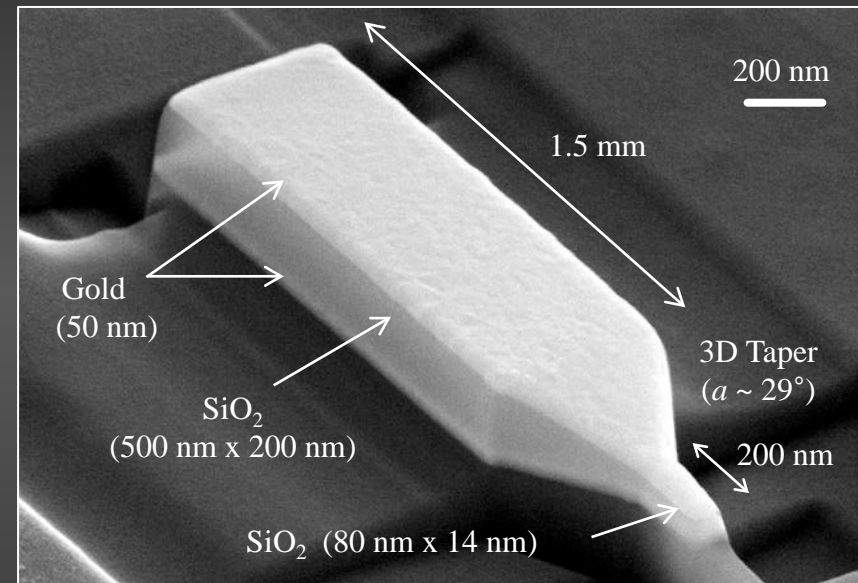
50-nm-Au deposition



Fabrications



3D MIM nanofocusing structure

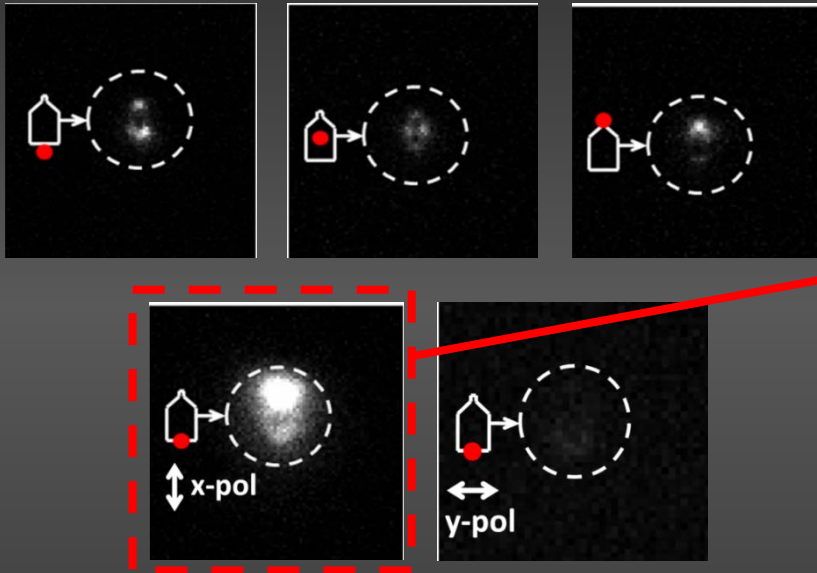


Minimum SiO₂ area = $14 \times 80 \text{ nm}^2$

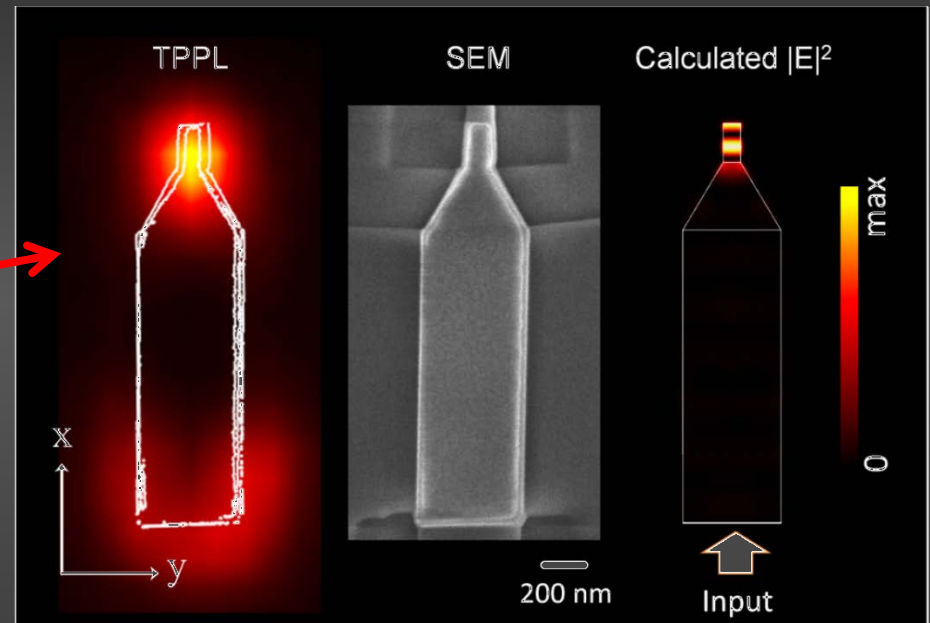
Tapering angle (a) = 29°

TPPL measurement

● : Laser-excitation location

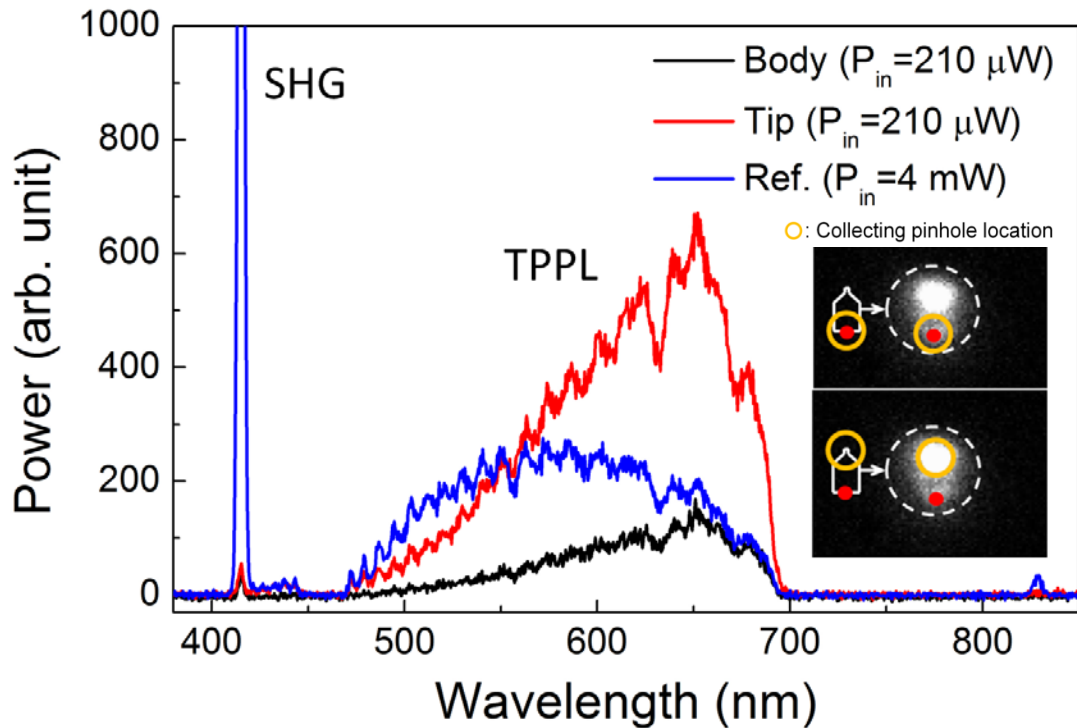


Unsaturated TPPL intensity map



Laser source: 120 fs Ti-sapphire laser at 830 nm
Time-averaged power = 210 μ W
Beam diameter \sim 400 nm (100 \times 0.90NA)

Estimation of E² Enhancement



E² enhancement

$$\alpha_{tip/body} = \alpha_{tip/inc} \alpha_{inc/body} \sim 400$$

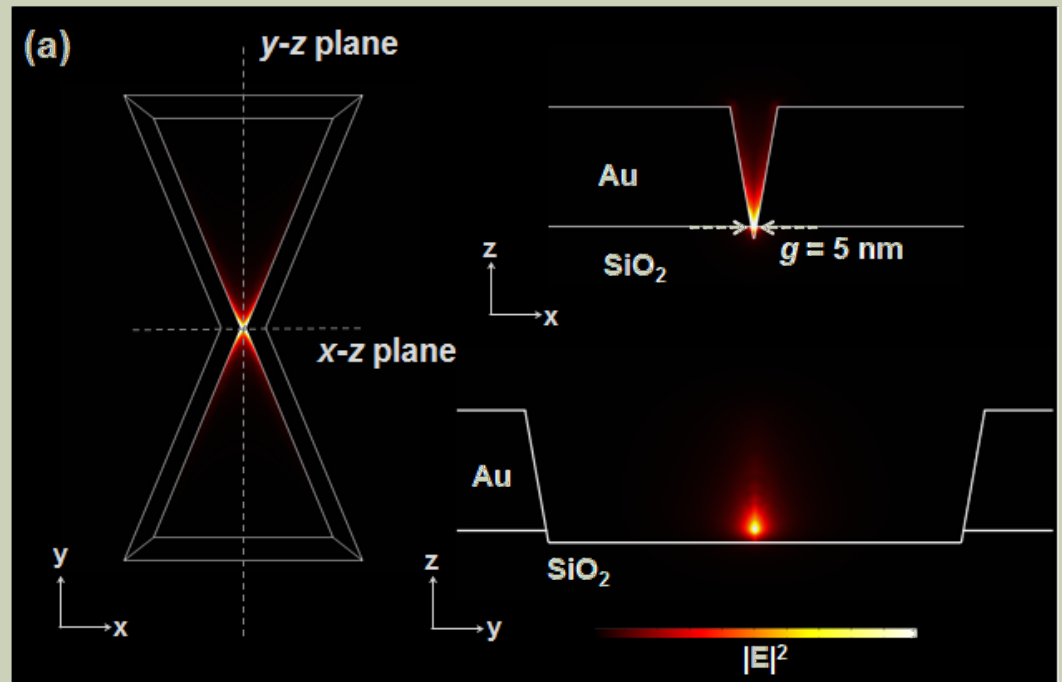
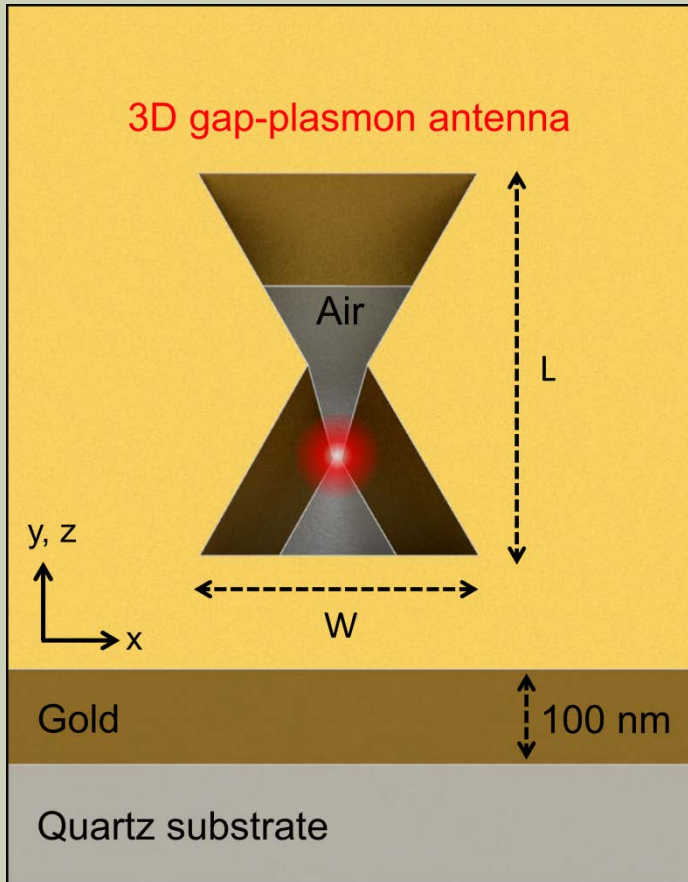
(cf. Simulation value = 410)

Estimated Transmittance ~ 74%

$$\alpha_{tip/inc} = \left(\frac{A_{ref}}{A_{tip}} \times \frac{\langle TPPL_{tip} \rangle}{\langle TPPL_{ref} \rangle} \right)^{1/2} \cdot \frac{\langle P_{ref} \rangle}{\langle P_{inc} \rangle} \approx 125$$

$$\alpha_{inc/body} = \left(\frac{1}{\eta} \right) \cdot \left(\frac{A_m^{body}}{A_{ref}} \right) \cdot \left(\frac{\epsilon_{SiO_2}}{n_{eff}^{body}} \right) \approx 3.2.$$

3-D POINT-LIKE CAVITY

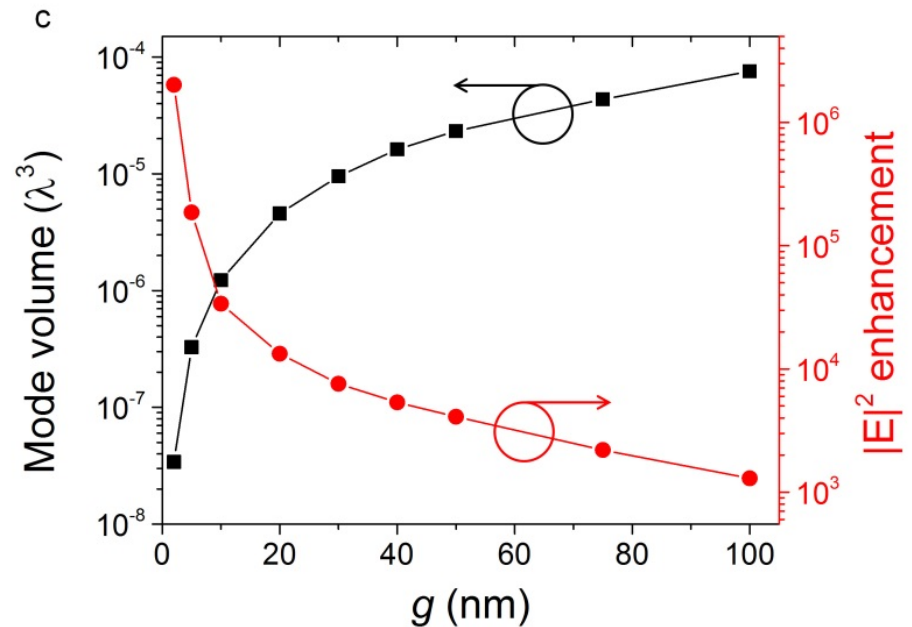
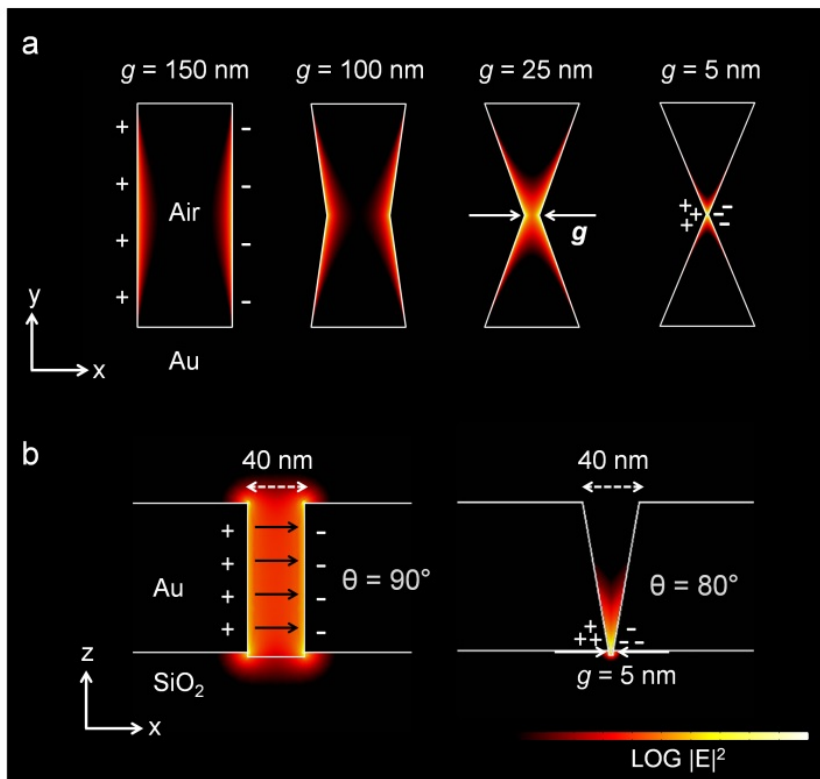


$$V_m = 1.3 \times 10^{-7} \lambda^3 (\sim 4 \times 10 \times 10 \text{ nm}^3)$$

$$|E|^2 \text{ enhancement} > 400,000$$

$$(\lambda = 1560 \text{ nm}, g = 4 \text{ nm}, L = 320 \text{ nm}, W = 100 \text{ nm})$$

3-D FIELD ENGINEERING & FIELD ENHANCEMENT

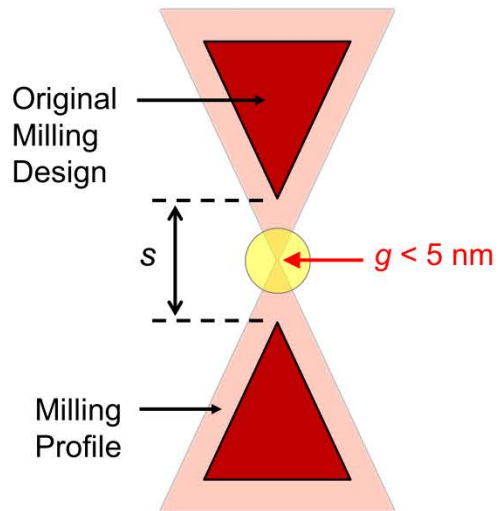


$$V_m = 1.3 \times 10^{-7} \lambda^3 (\sim 4 \times 10 \times 10 \text{ nm}^3)$$

$|E|^a$ enhancement $> 400,000$ @ $g = 4 \text{ nm}$

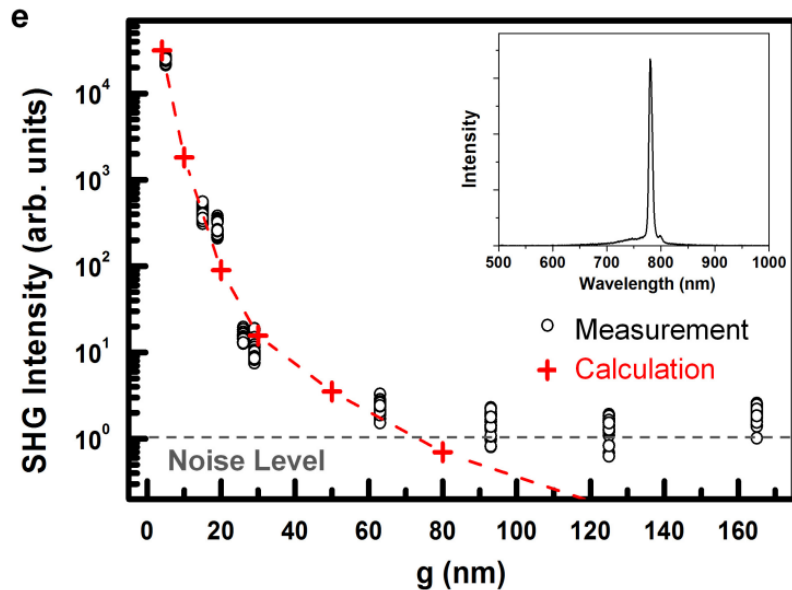
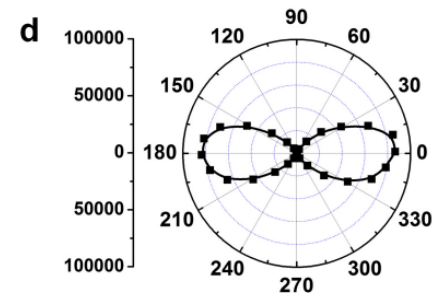
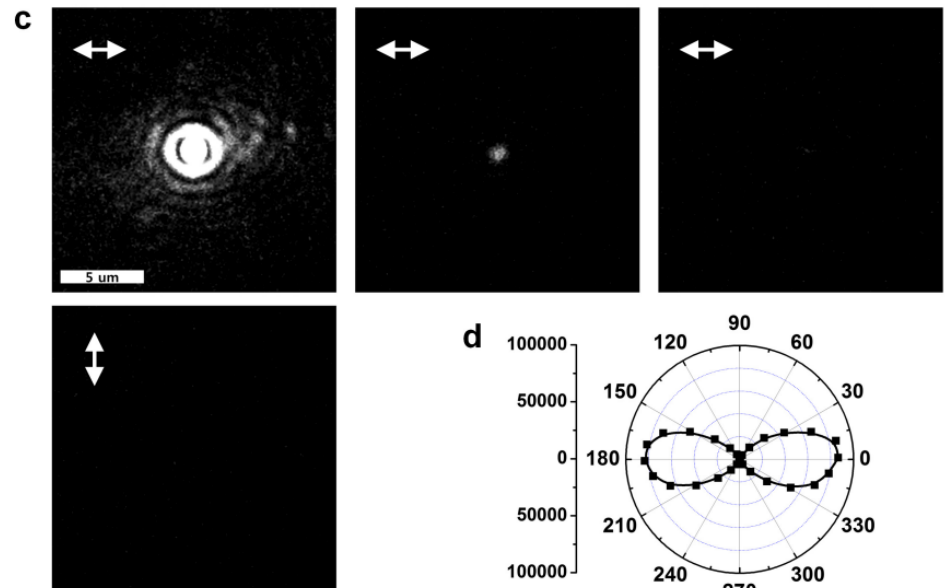
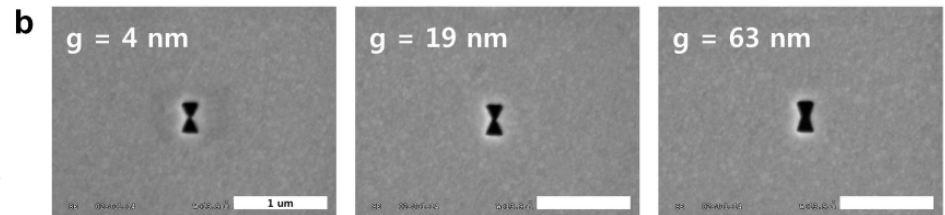
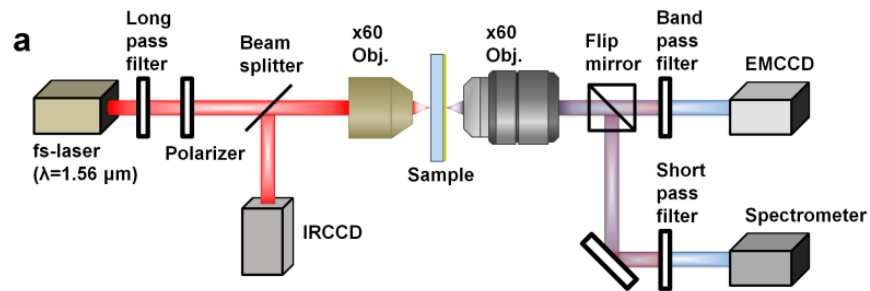
PROXIMAL FIB MILLING TECHNIQUE

a



STRONG FIELD ENHANCEMENT

From a 4 nm-gap antenna, a nonlinear second-harmonic signal more than 27,000-times stronger than that from a 100 nm-gap antenna is observed.

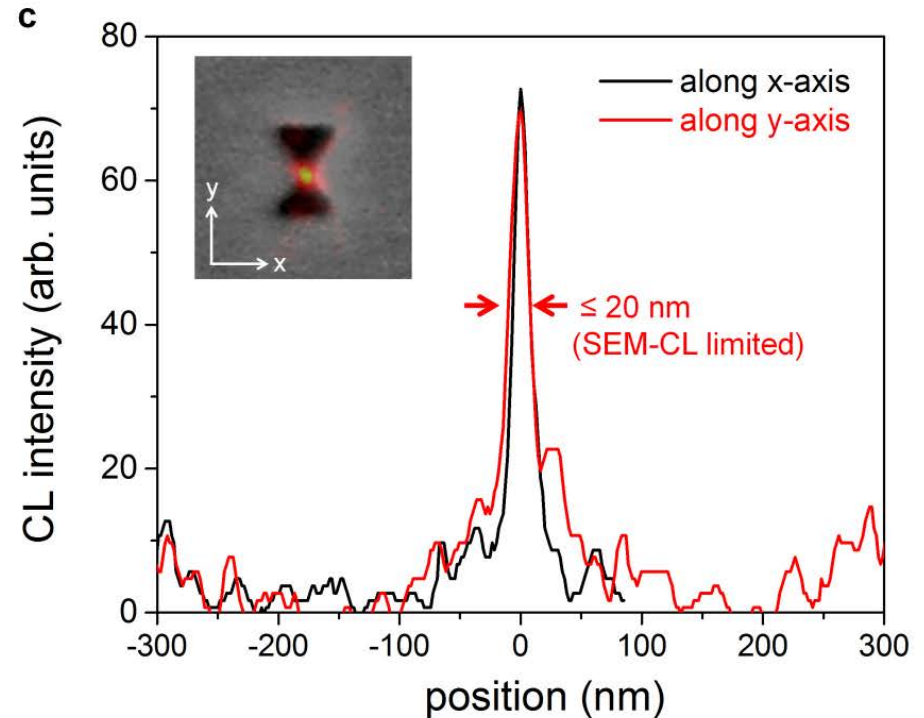
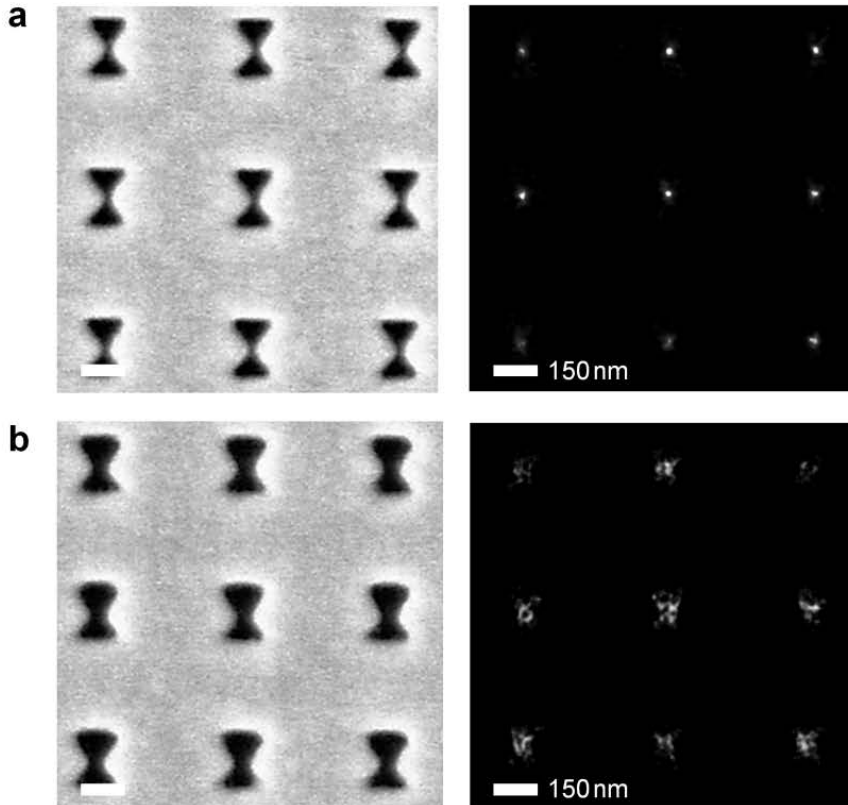


EXTREME FIELD CONFINEMENT

Scanning cathodoluminescence images confirm unambiguous photon confinement in a resolution-limited area $20 \times 20 \text{ nm}^2$ on top of the nano gap.

SEM image

SEM-CL image

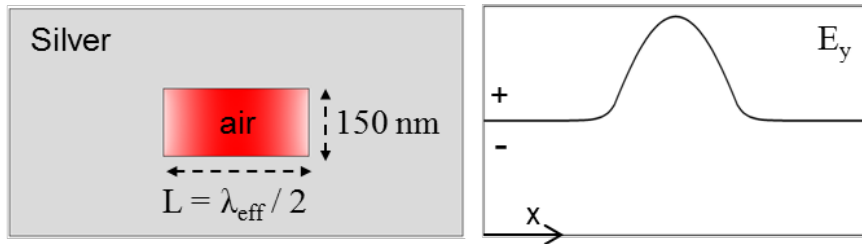


**GEOMETRIC ENGINEERING
FOR EFFICIENT COUPLING**

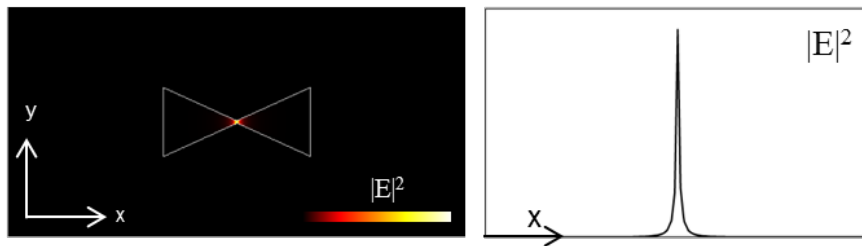
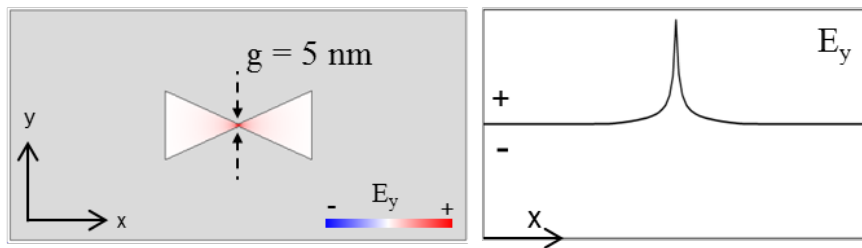
Double-Nano-Gap Plasmon Antenna

(a)

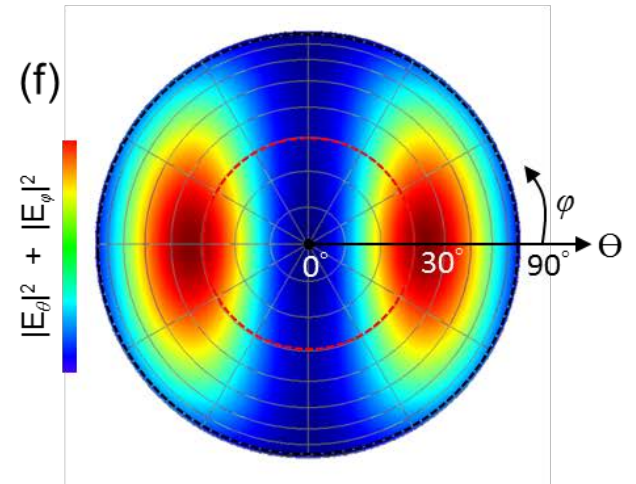
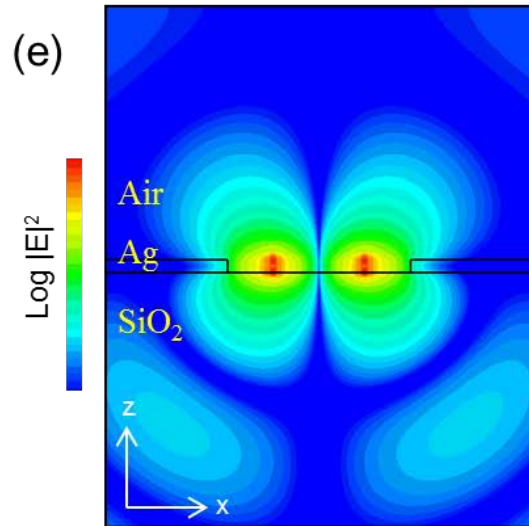
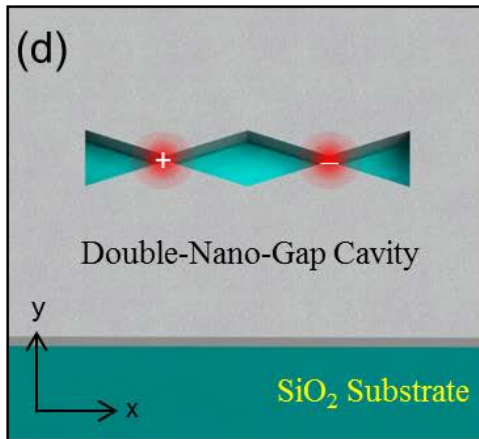
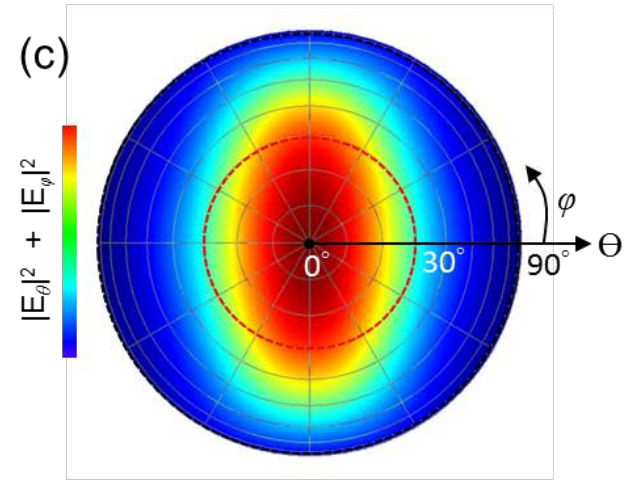
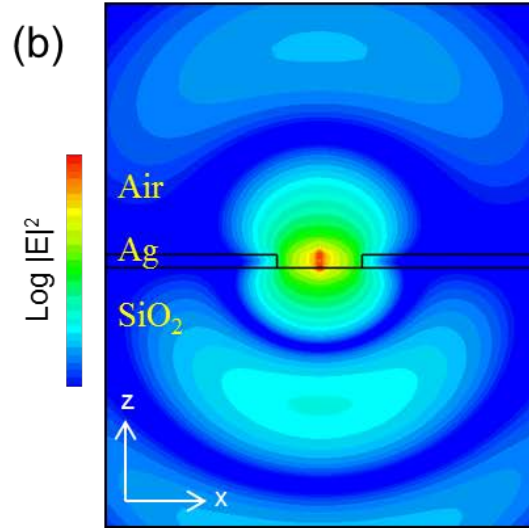
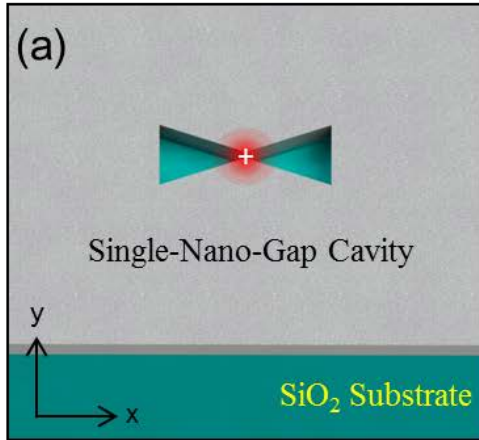
1st mode



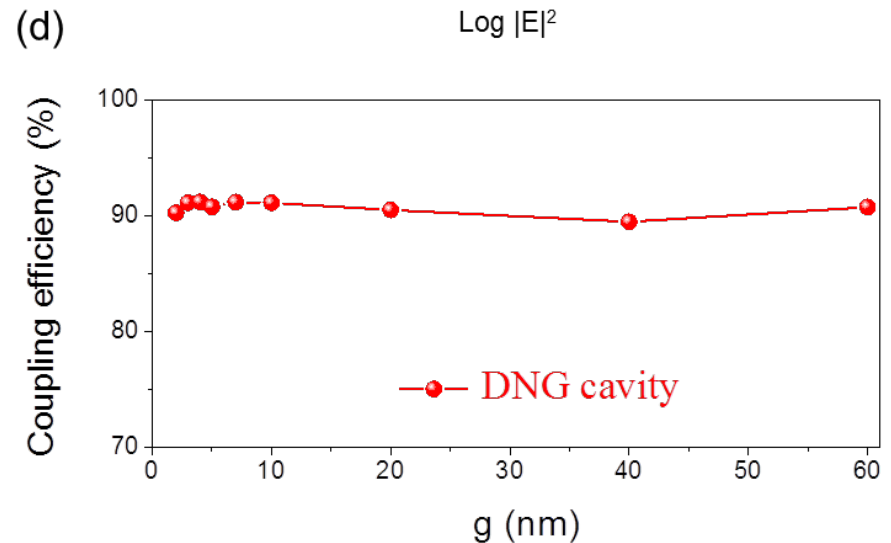
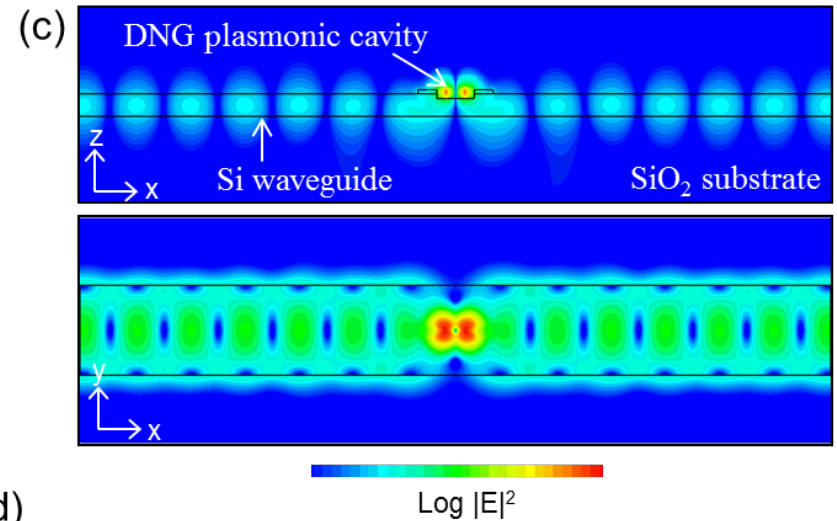
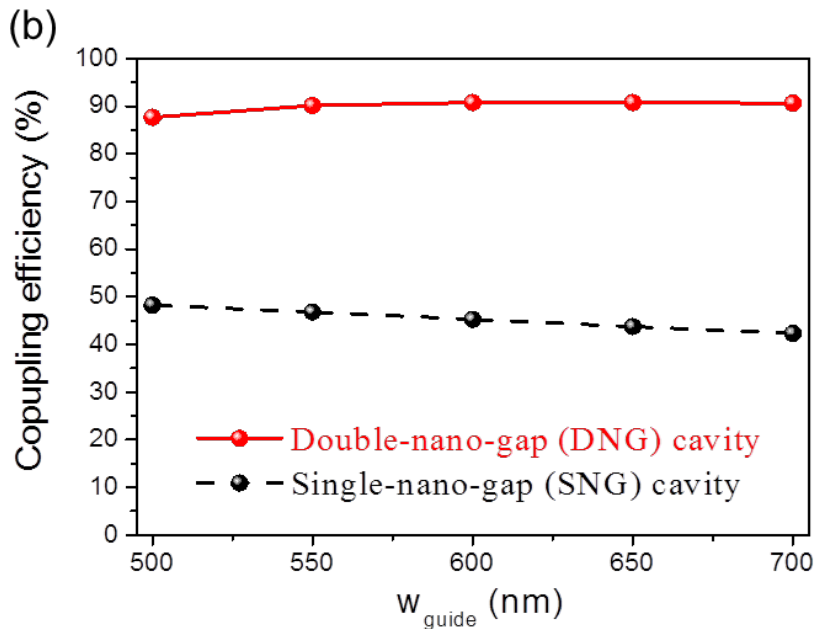
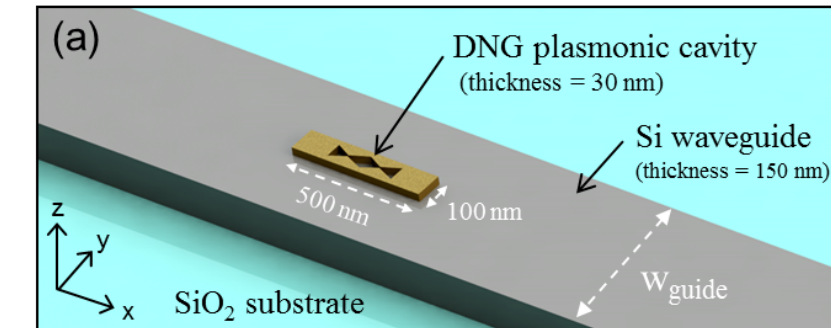
(b)



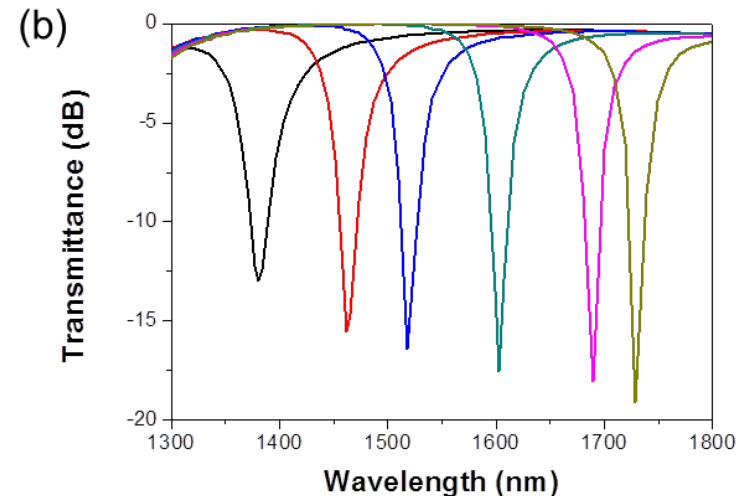
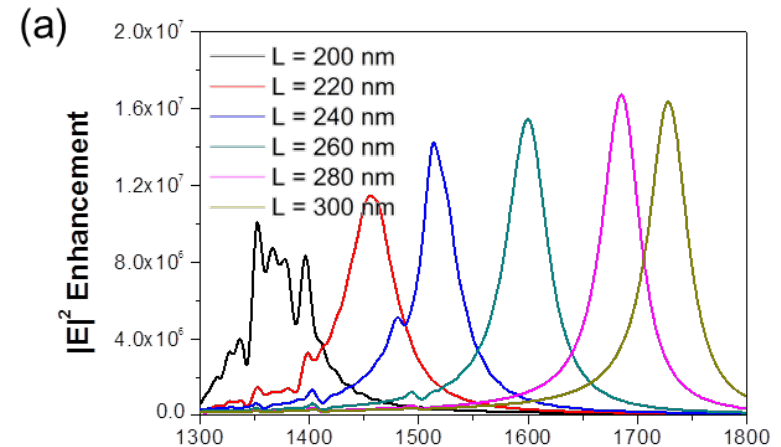
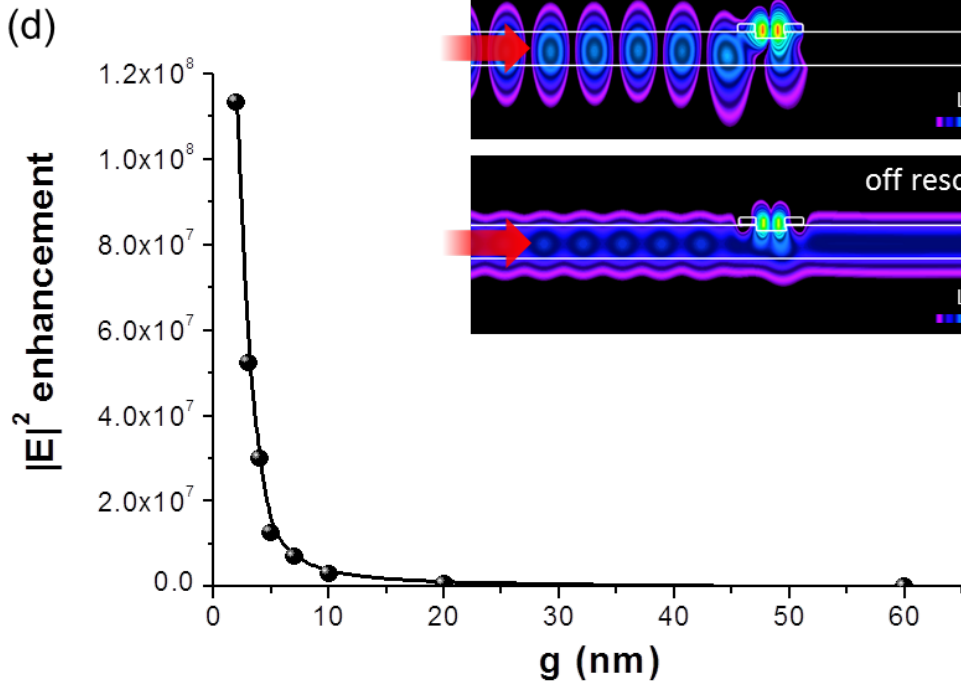
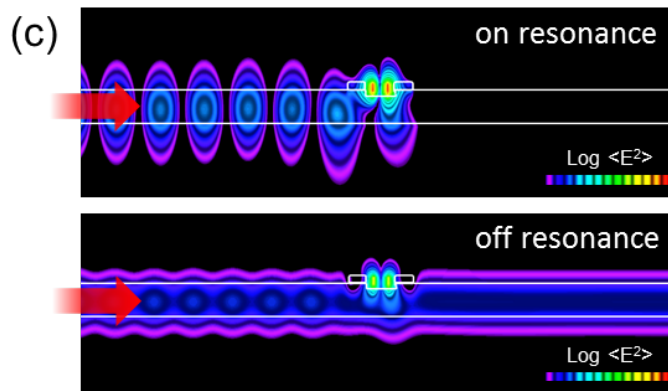
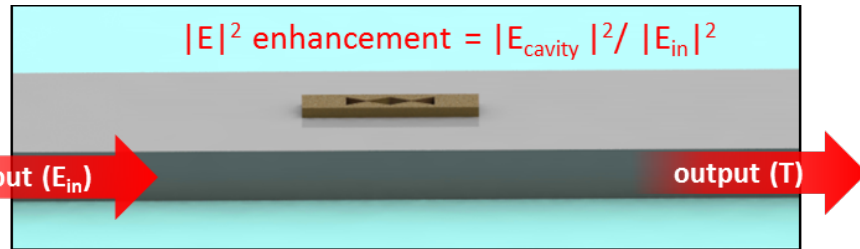
Far-field Radiation Patterns



Gap-Plasmon Antenna Coupled with Si waveguide



Extreme Field Enhancement

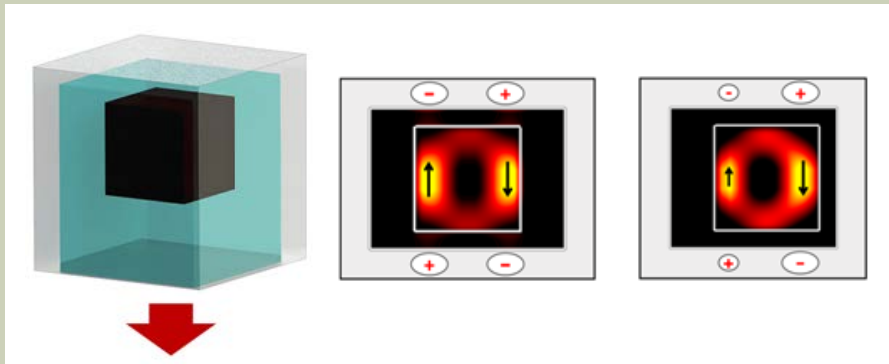


SUMMARY

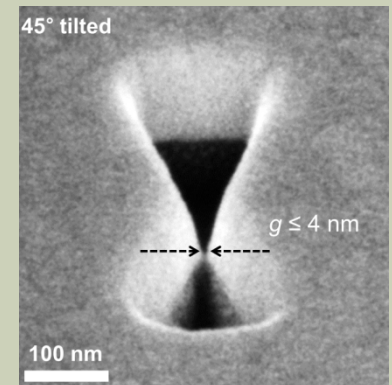
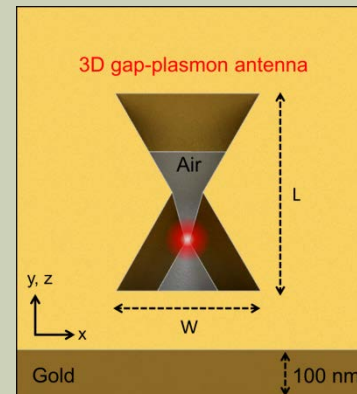
Sub-wavelength Plasmonic Cavities

Plasmonic Engineering

Cladding Engineering



Geometric Engineering





KAIST



Prof.
Myung-Ki Kim



Prof.
Yong-Hee Lee



Young-Ho Jin



Seung Ju Yoon



Byoung Jun Park



Jungmin Lee



Nu-Ri Park



SAMSUNG